

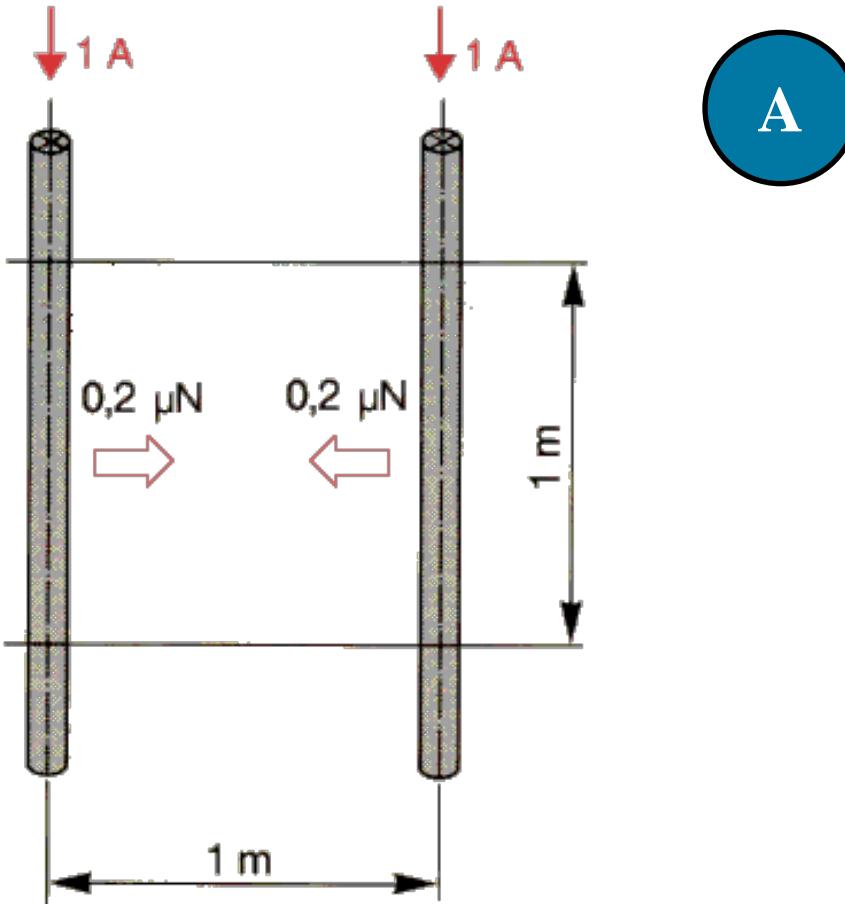
Investigation of dynamic quantum dot initialization by electron counting

Lukas Fricke

Overview

- Introduction to dynamic quantum dots → electron pumping
- Characterization of a dynamic dot by charge detection
- Series operation of 3 pumps with charge detectors

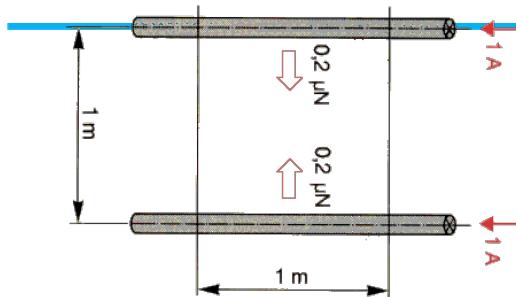
Electrical units



SI base unit: Ampere (A)

- present **definition**: force between wires
- not used for **realisation**

Electrical units



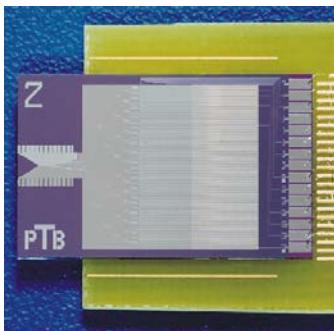
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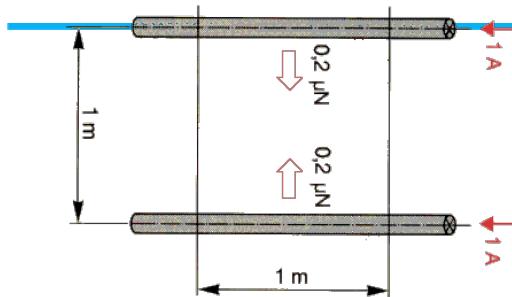
Volt (V)

- realised by Josephson effect
- fixed proportionality:
 $2e/h = 483\,597.9X$ GHz/V

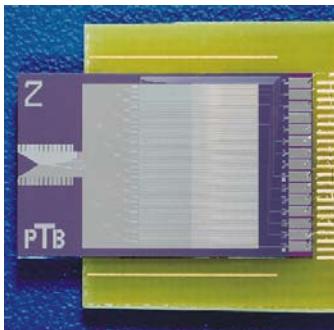


$$U = n \cdot \frac{h}{2e} \cdot f$$

Electrical units

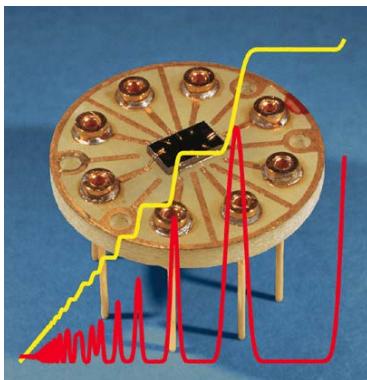


A



$$U = n \cdot \frac{h}{2e} \cdot f$$

V



$$R_H = \frac{1}{n} \frac{h}{e^2}$$

Ω

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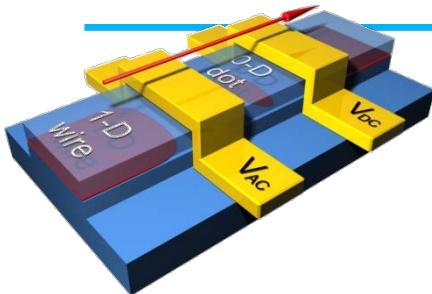
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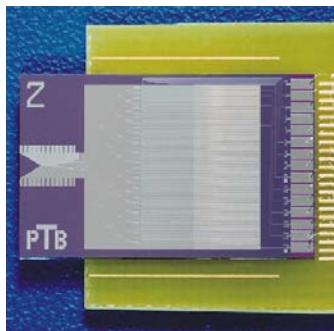
Ohm (Ω)

- quantum Hall effect
- $h/e^2 = 25\,712.807\text{X}\text{ Ω}$

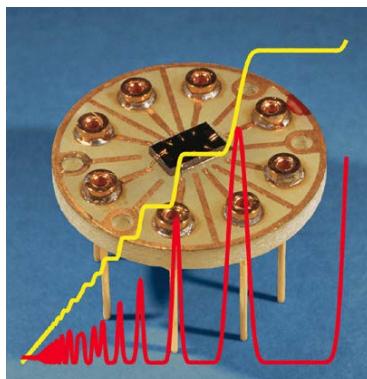
Electrical units



$$I = n \cdot e \cdot f$$



$$U = n \cdot \frac{h}{2e} \cdot f$$



$$R_H = \frac{1}{n} \frac{h}{e^2}$$



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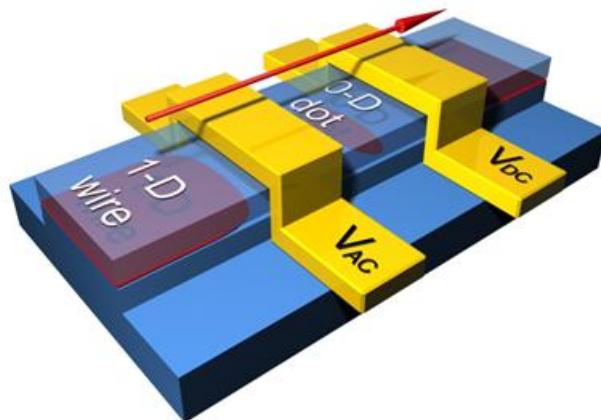
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new Ampere (A):

$$1\text{ A} = 6.24150X \cdot 10^{18} \text{ e / 1s}$$

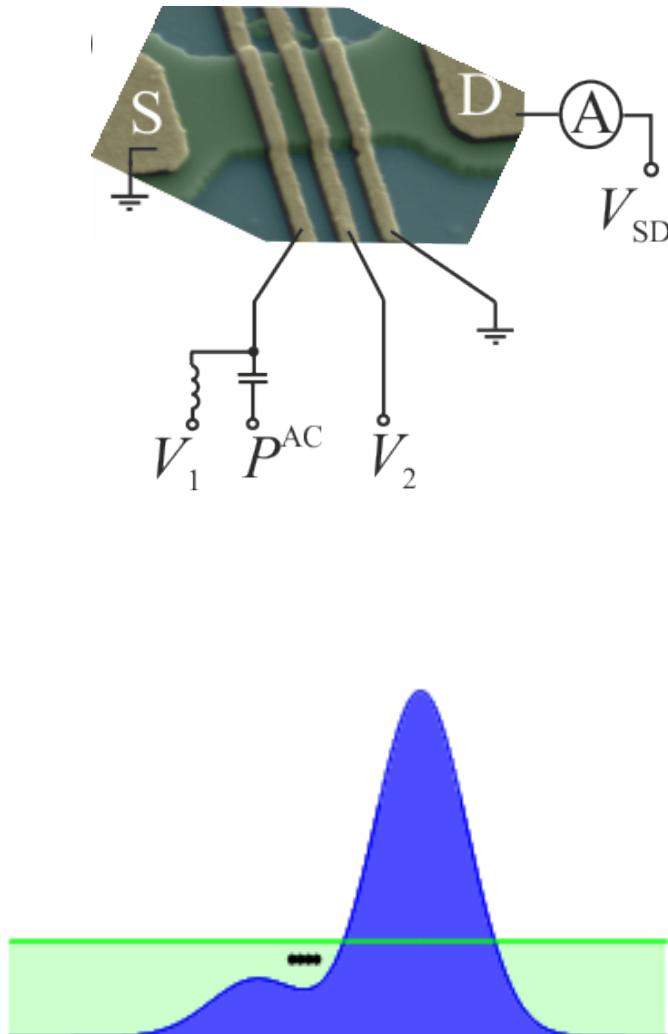
- fix elementary charge e
- quantised electron pumping

Non-adiabatic quantum dot



- GaAs/AlGaAs 2D electron gas channel
 - Top gates define quantum dot
 - Modulation of entrance barrier
 - Capture electrons from source
 - Lift electrons over exit barrier
 - Directed pumping without bias
 - Quantized current: $I = e \cdot f$
-
- Advantages:
 - GHz frequencies
→ high currents
 - Prospect for high precision
 - Simple device & operation
→ Parallelization

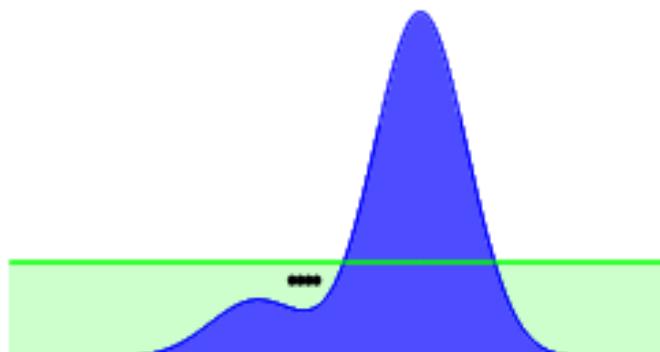
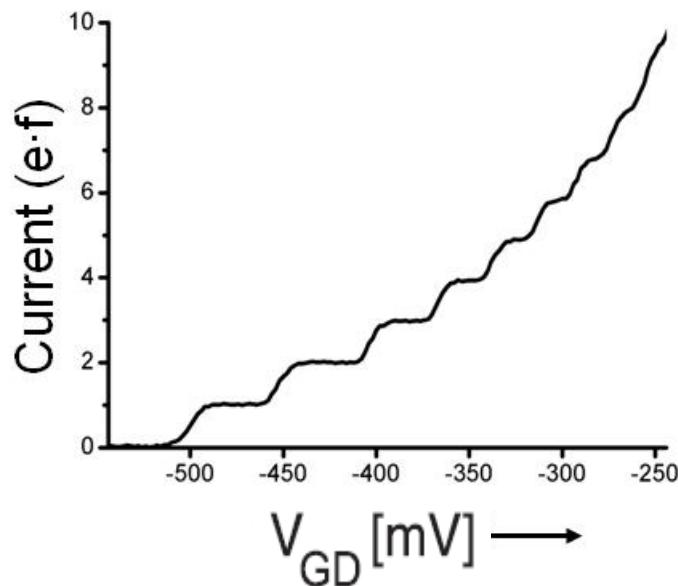
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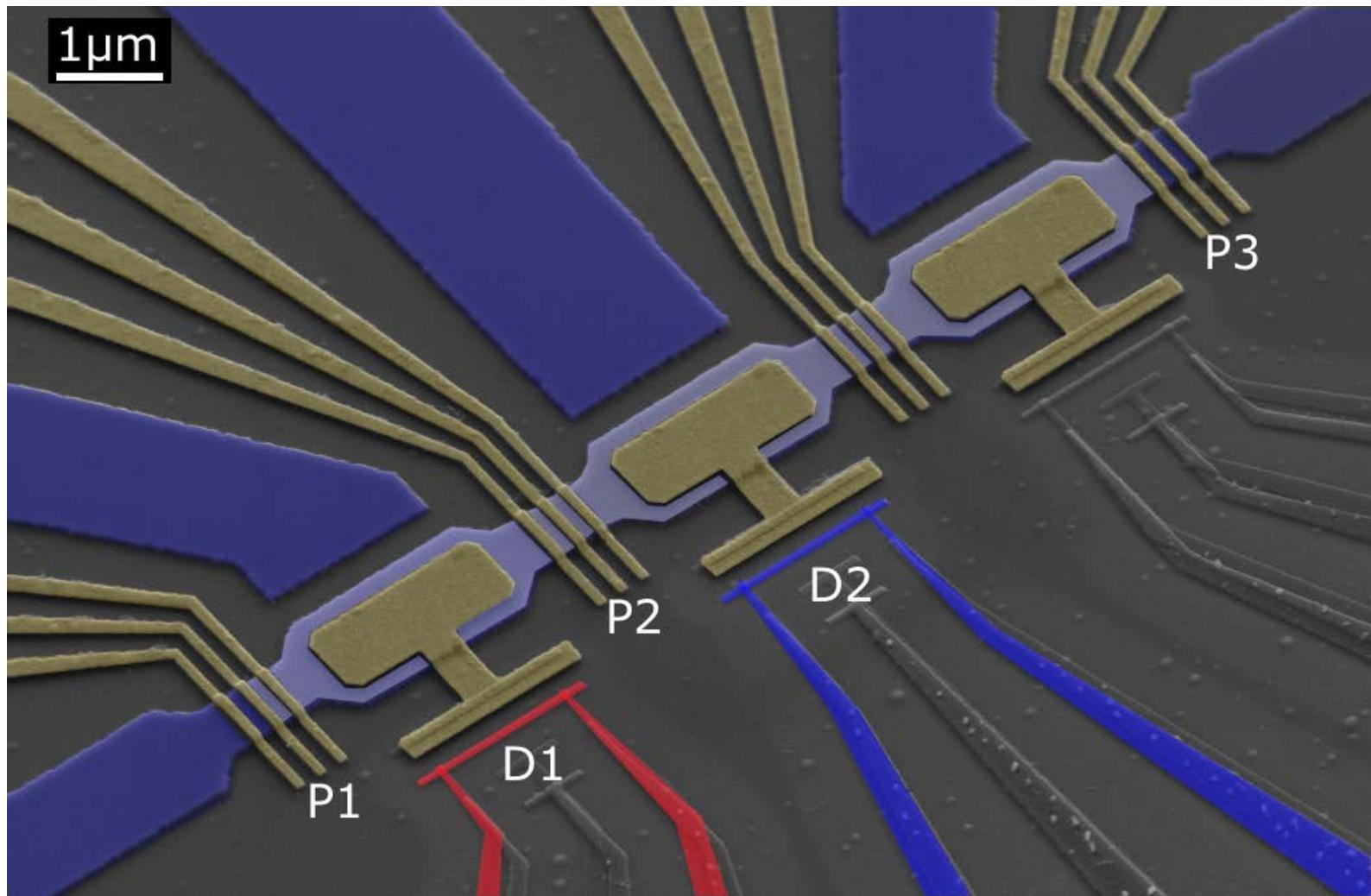
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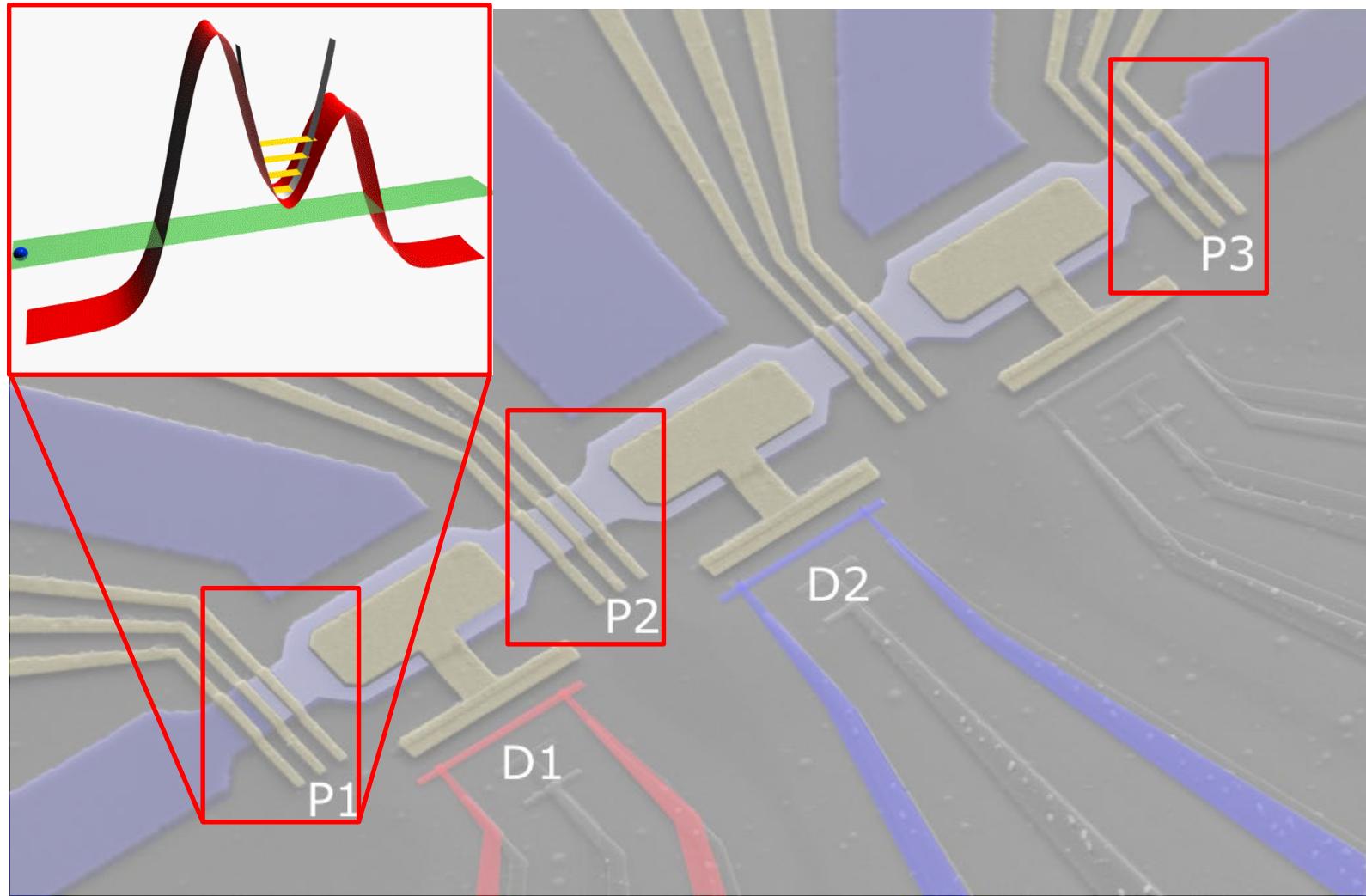
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Device under investigation



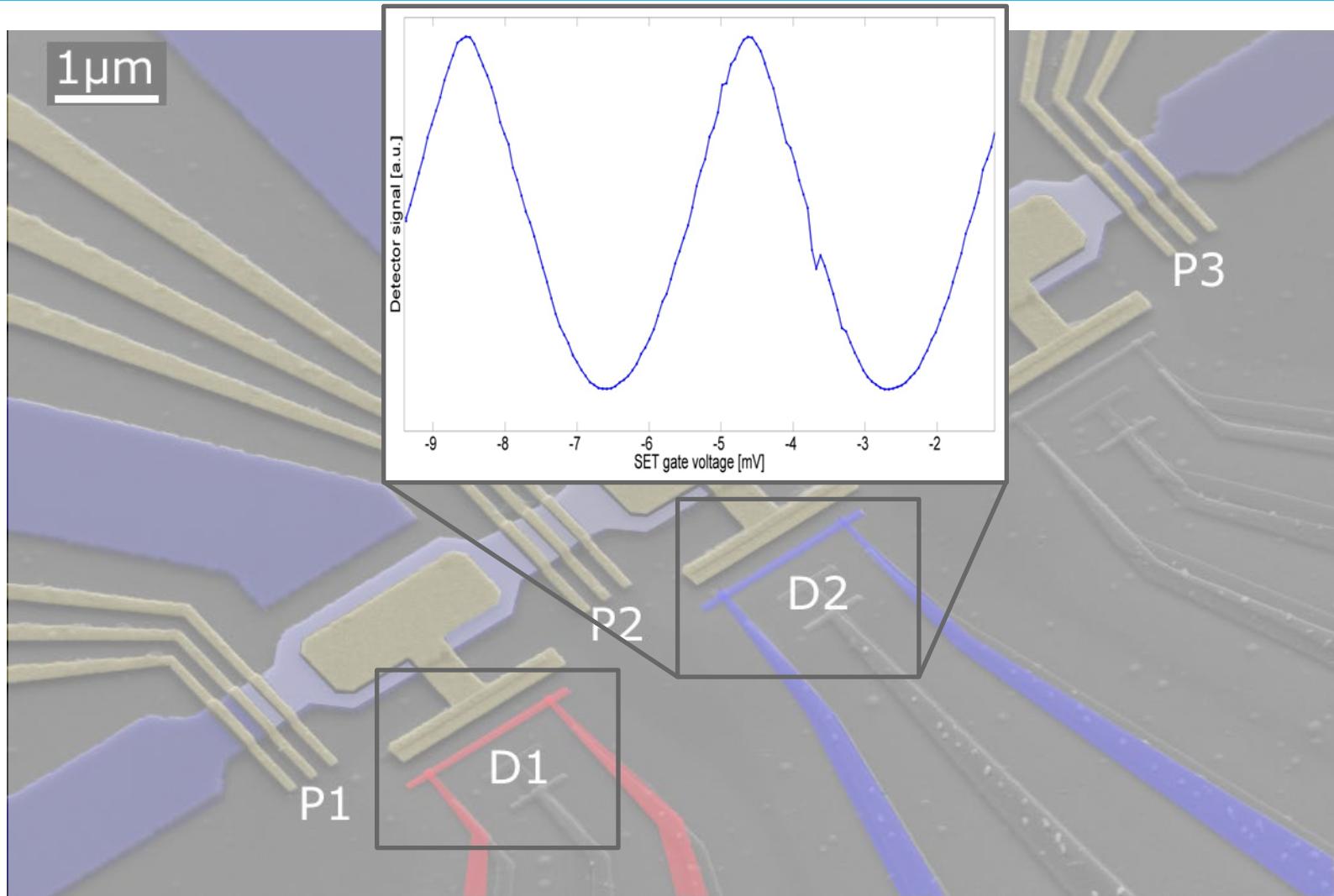
Device under investigation



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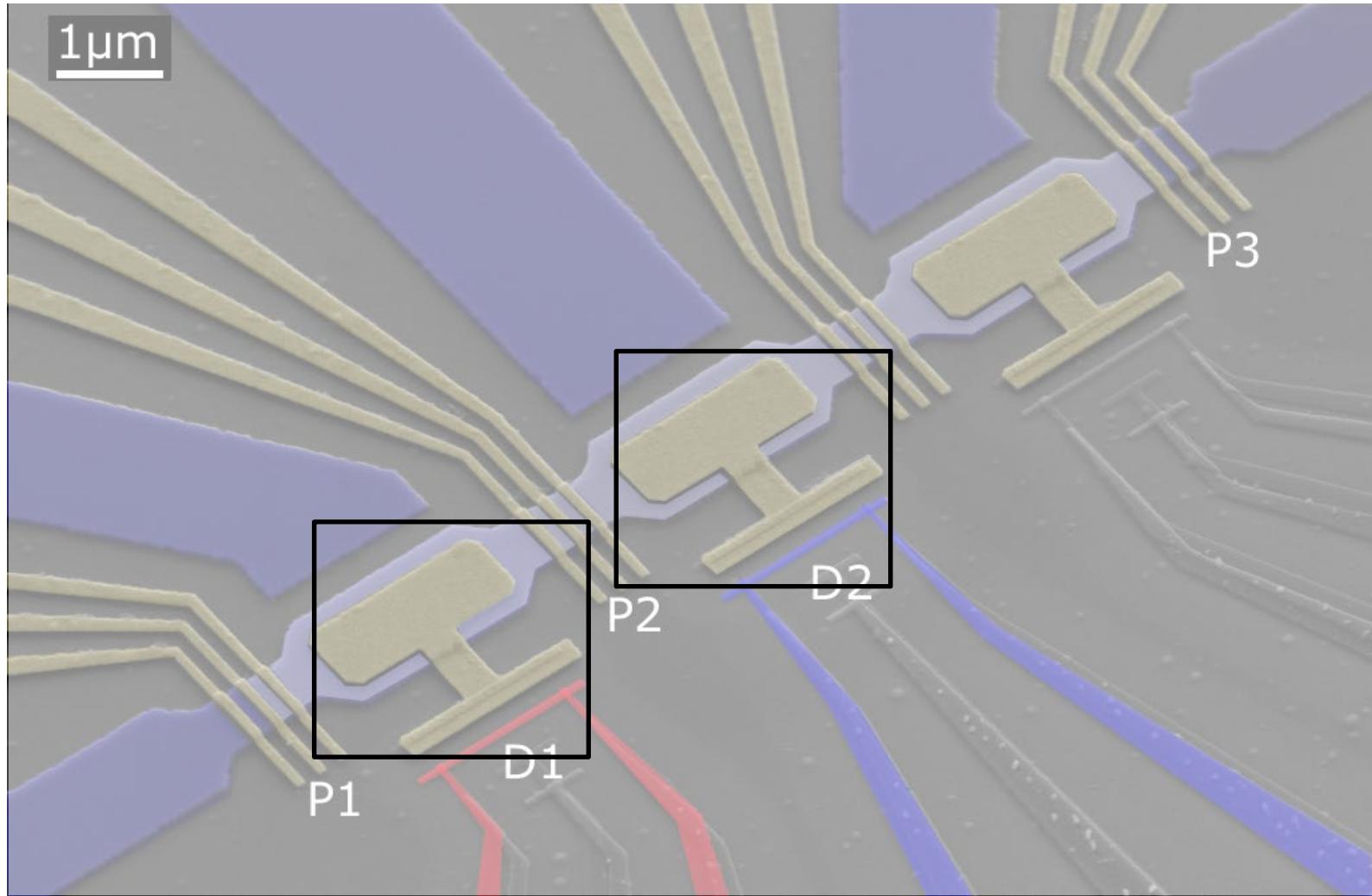
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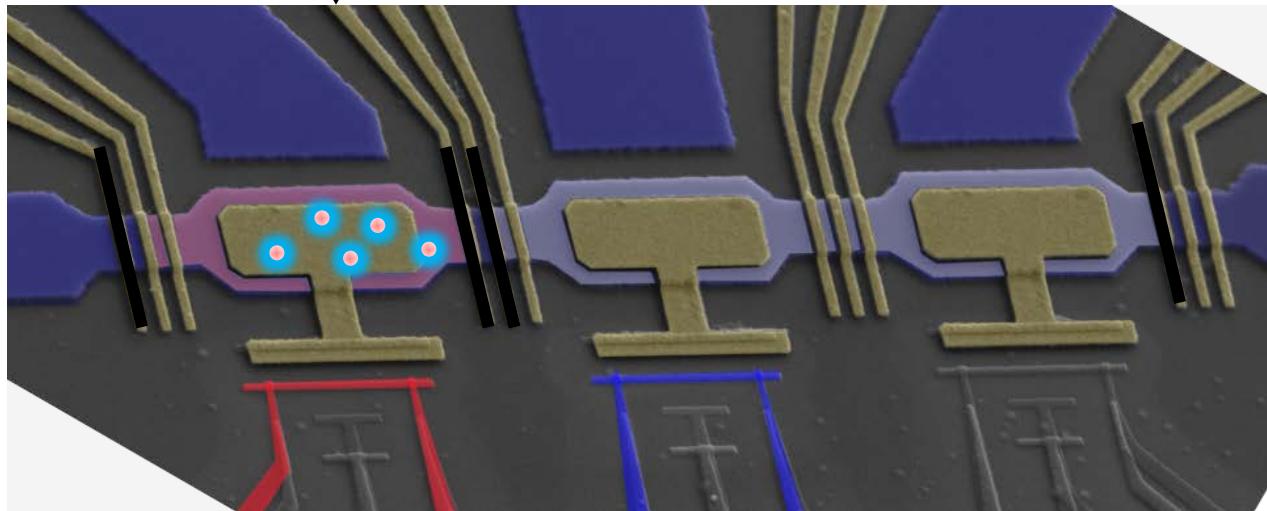
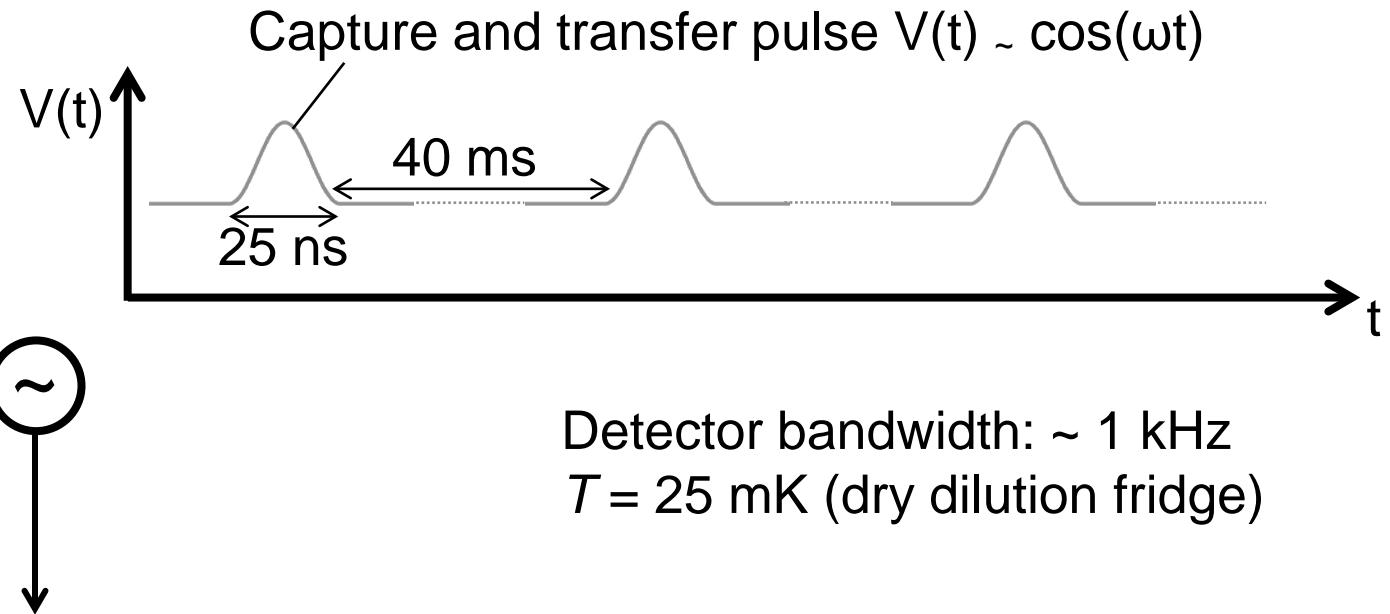
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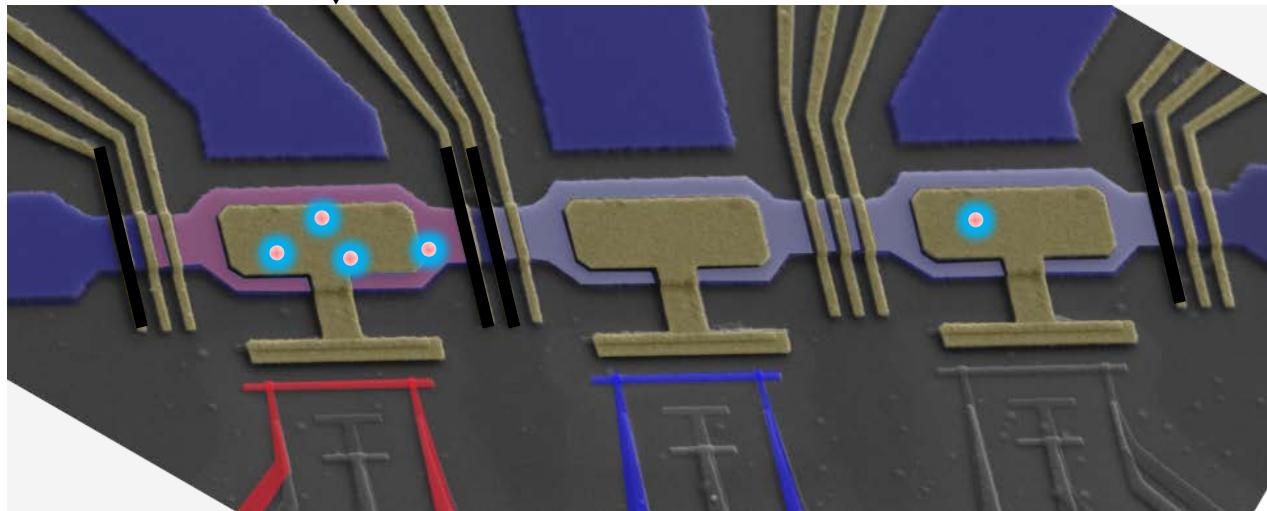
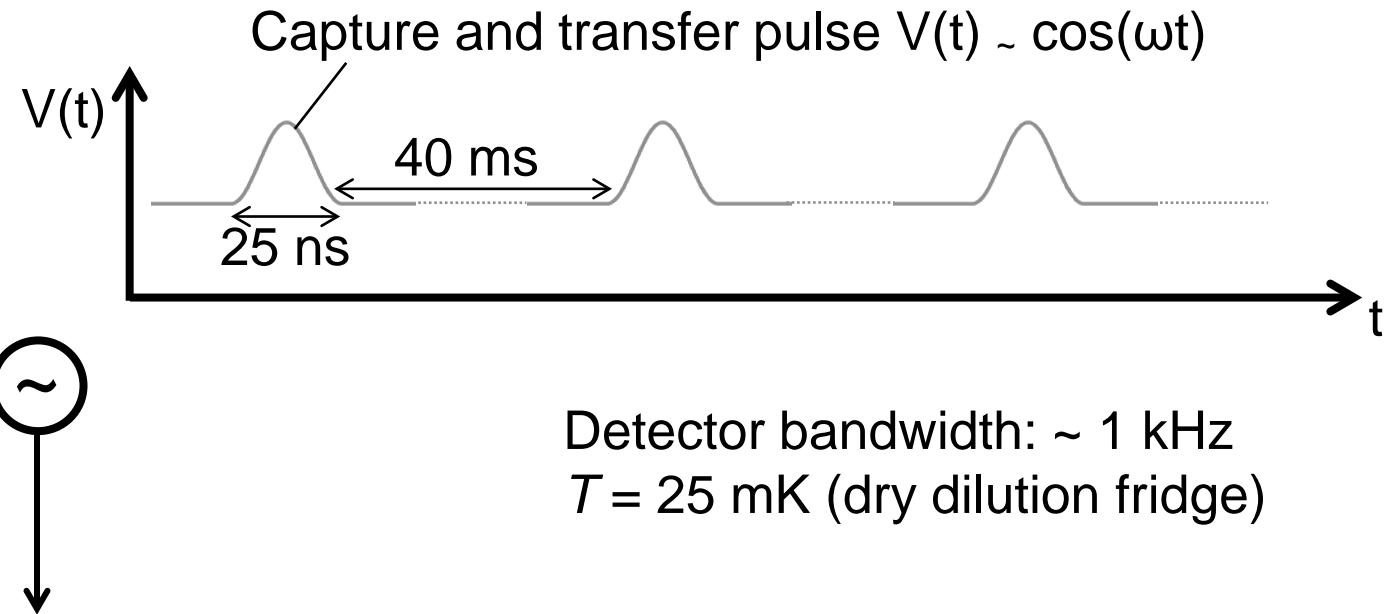
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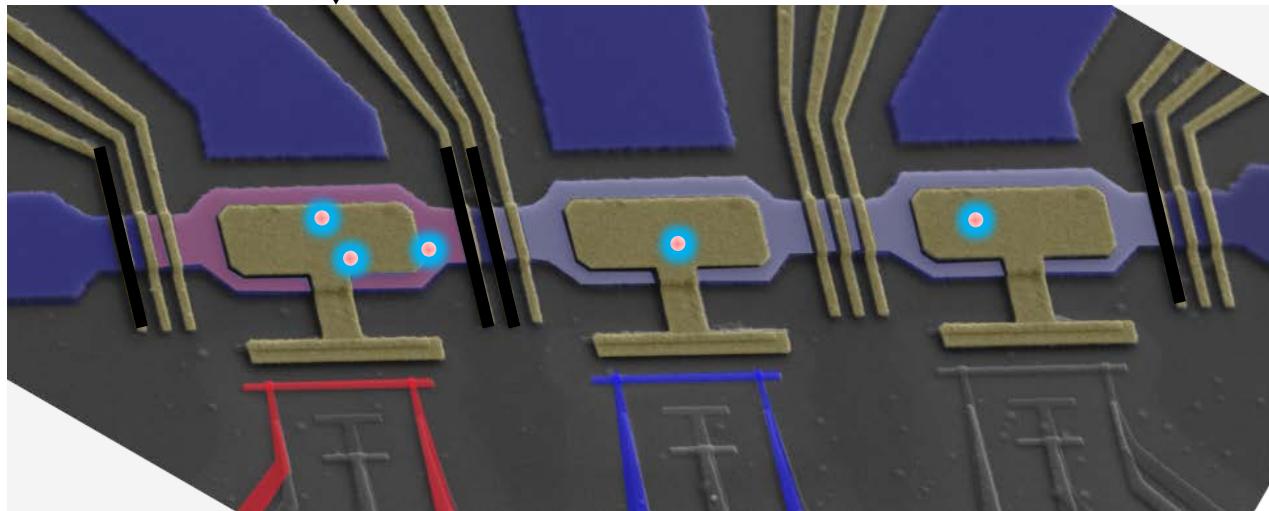
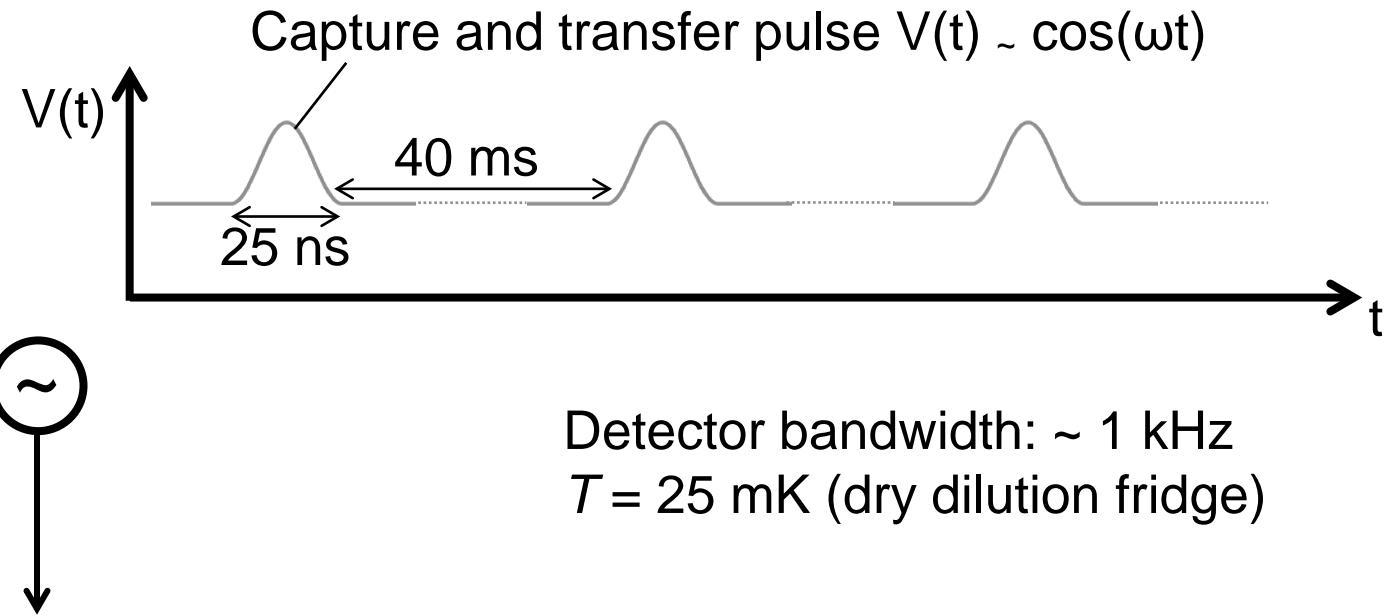
Single-charge transfer between nodes



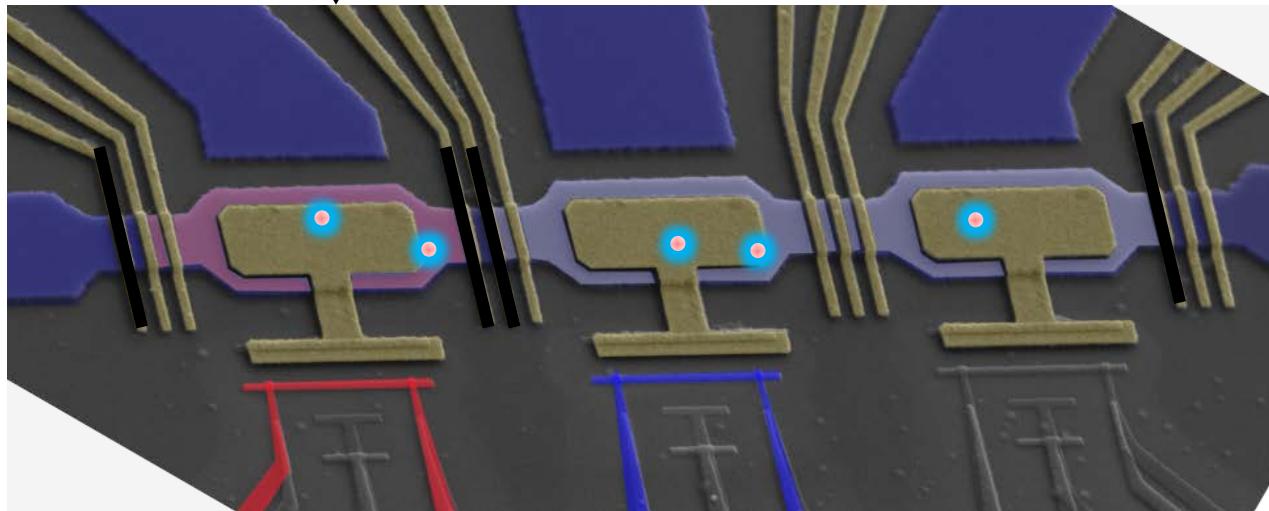
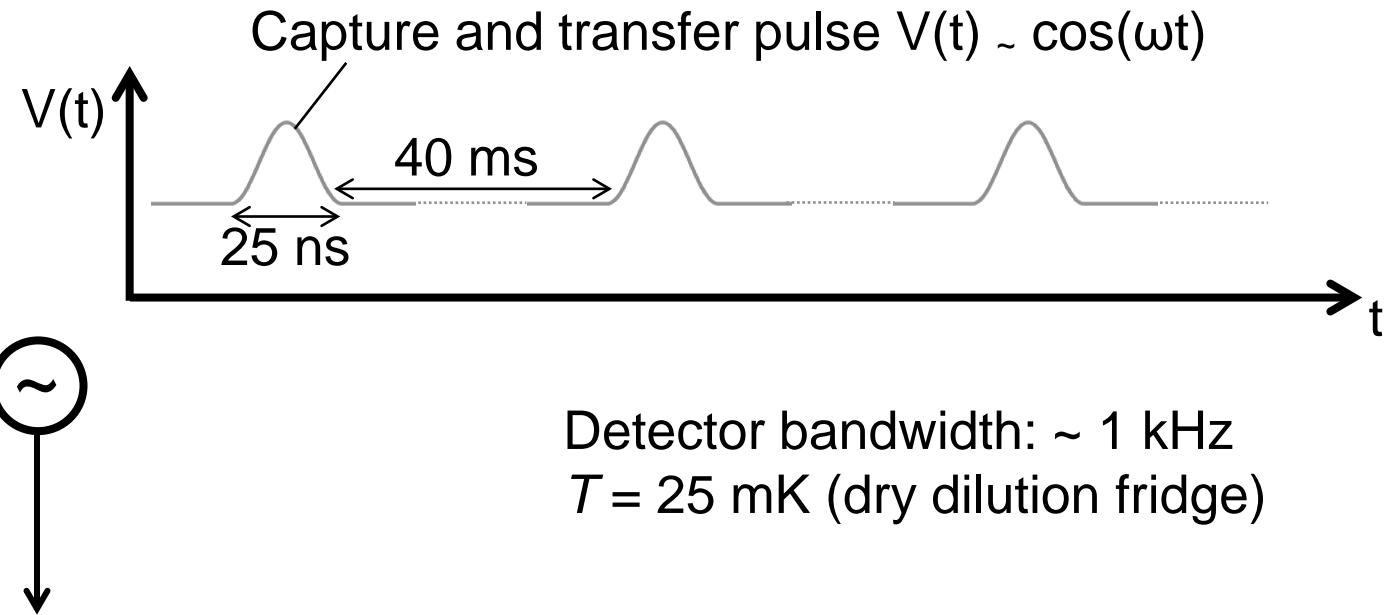
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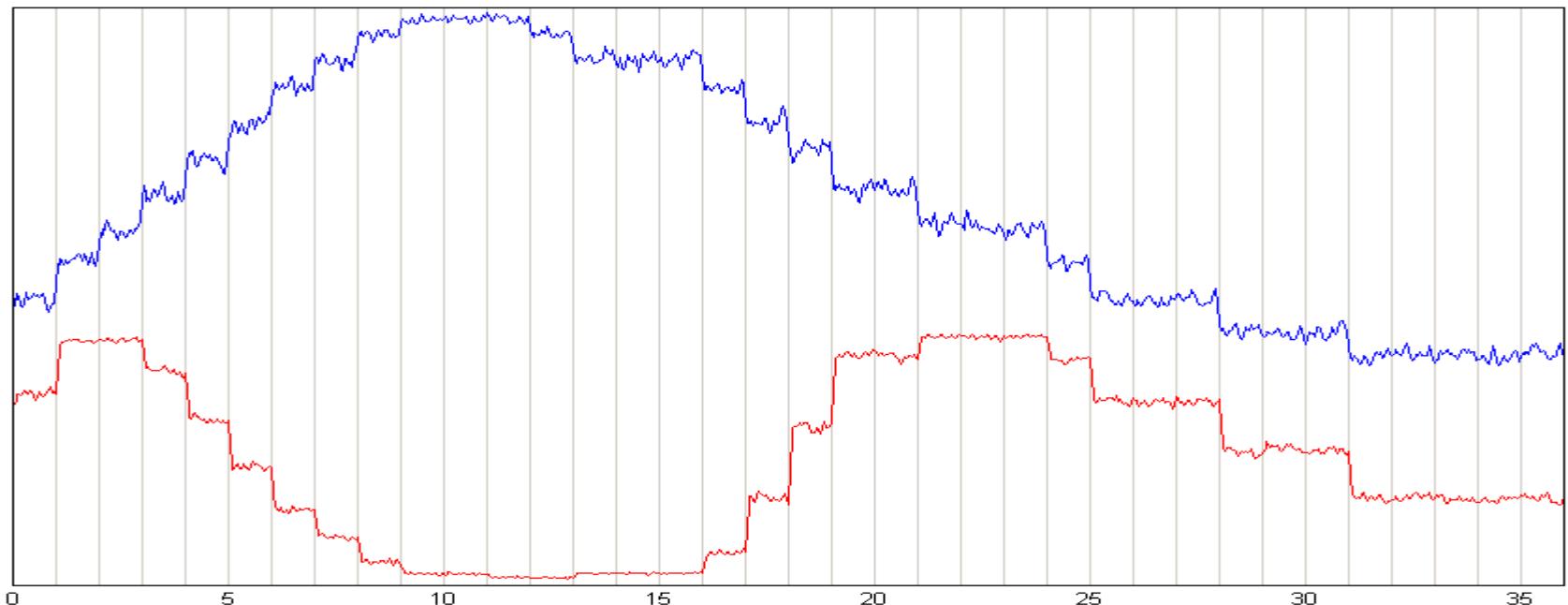
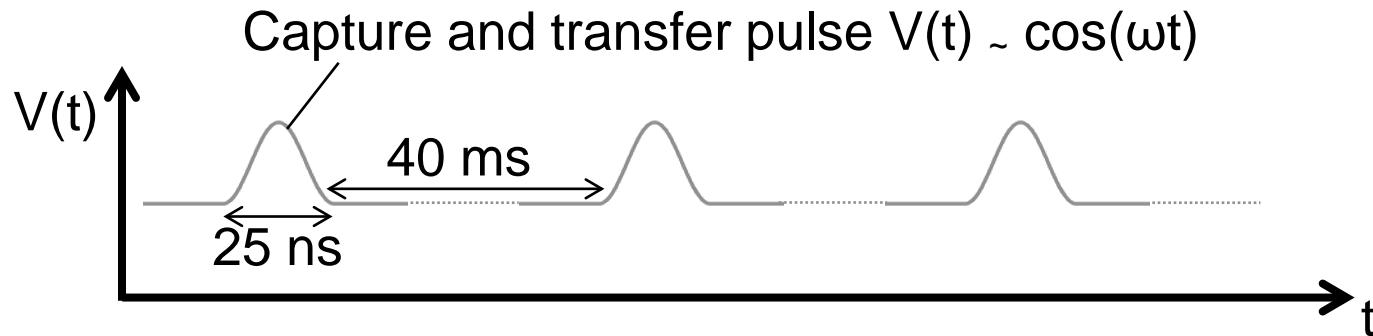
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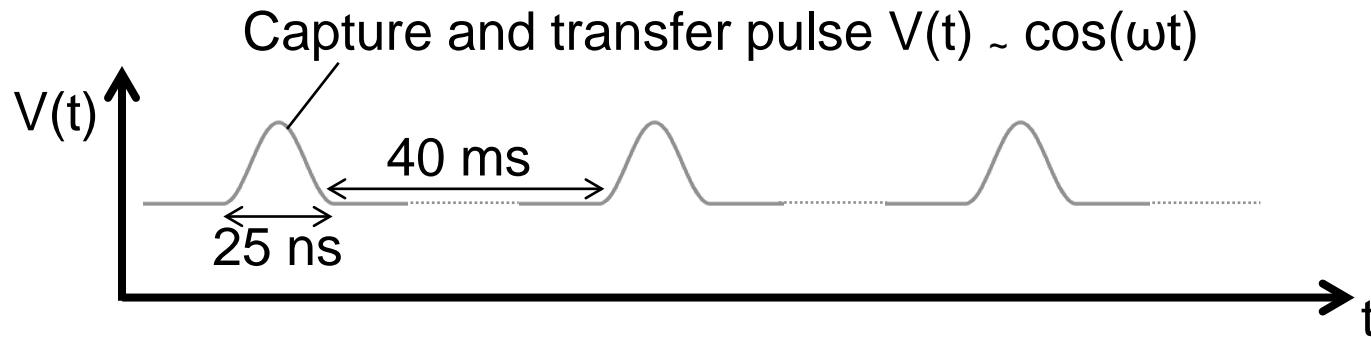
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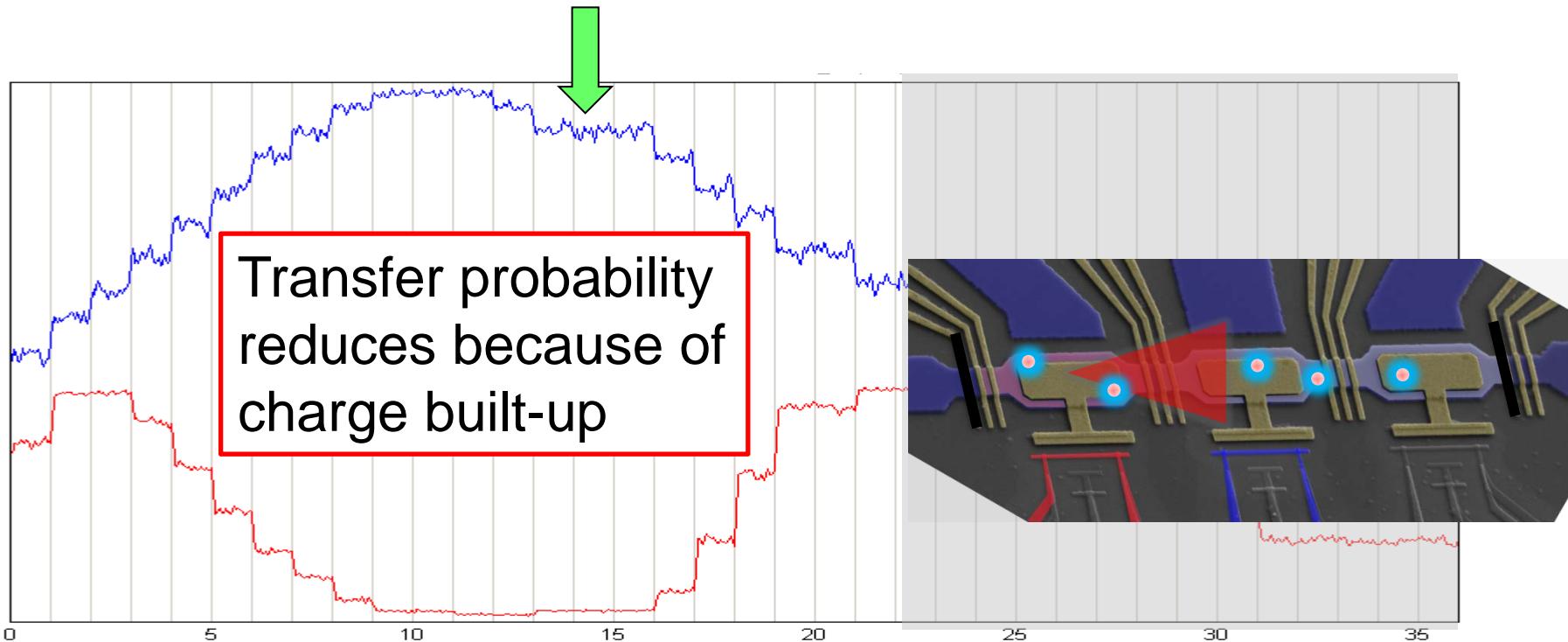
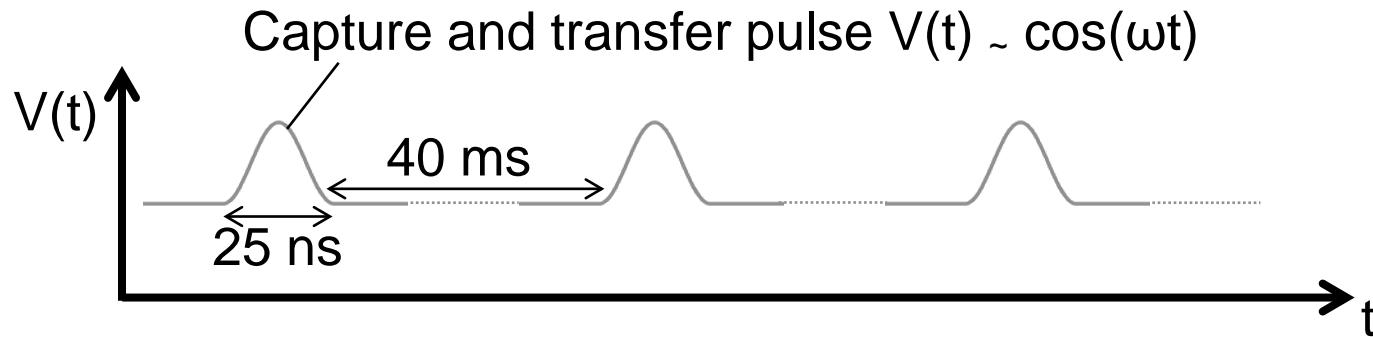
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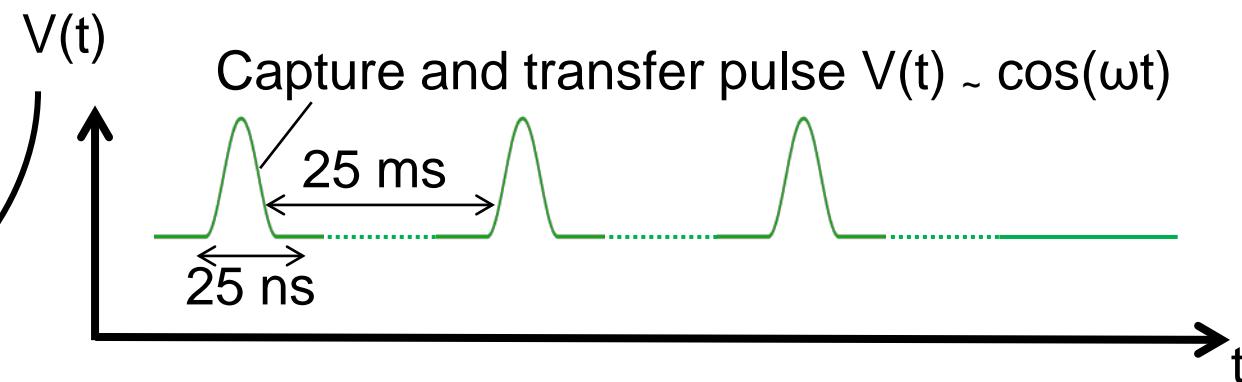
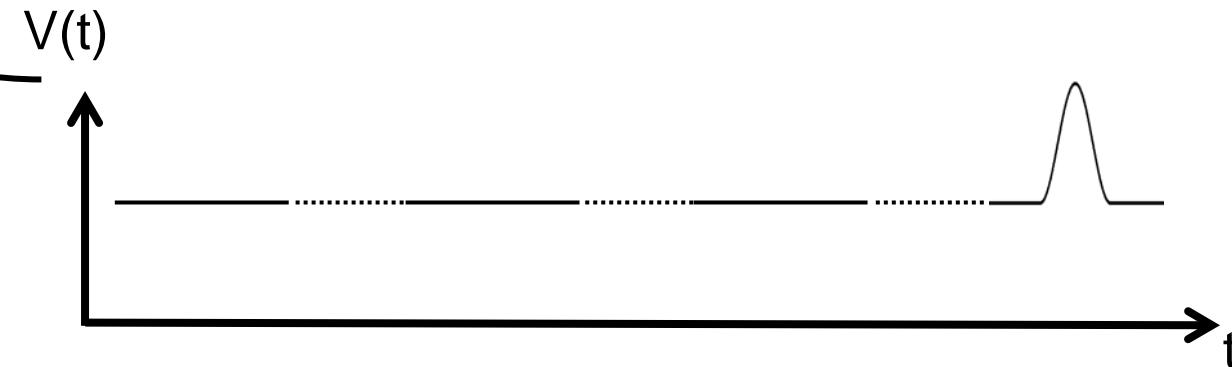
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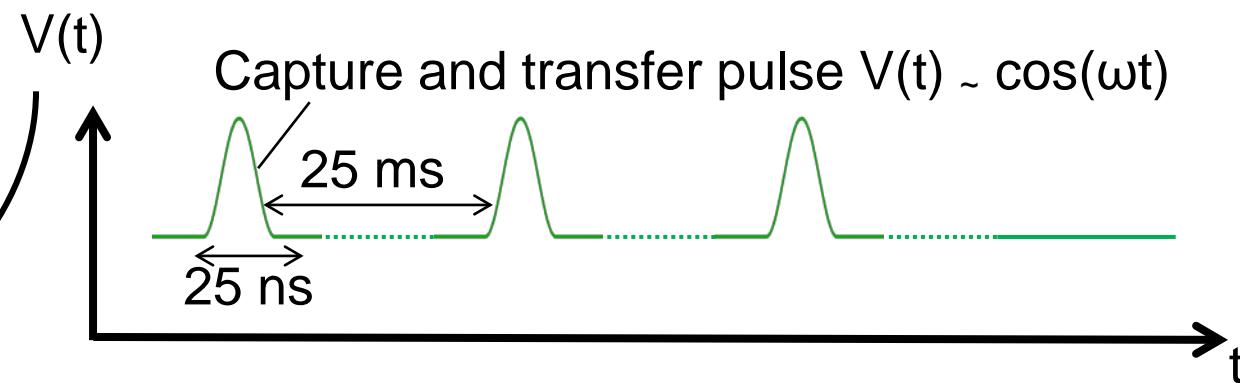
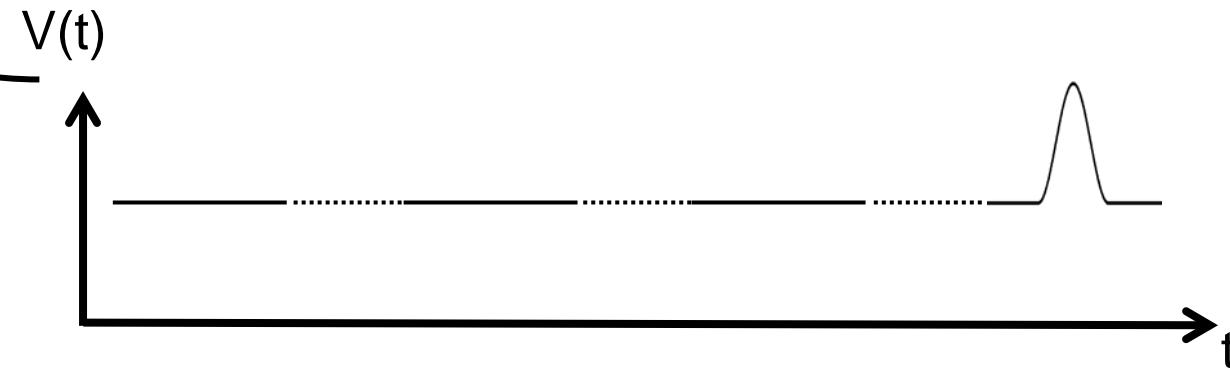
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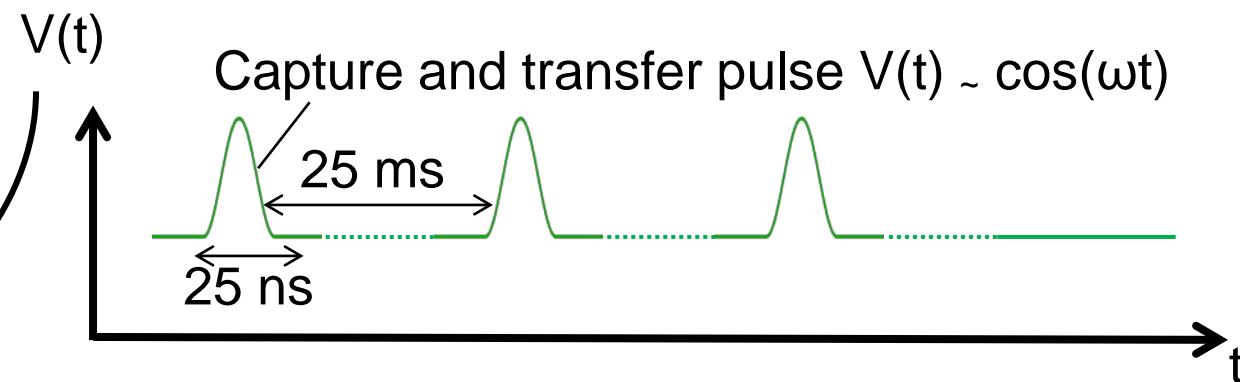
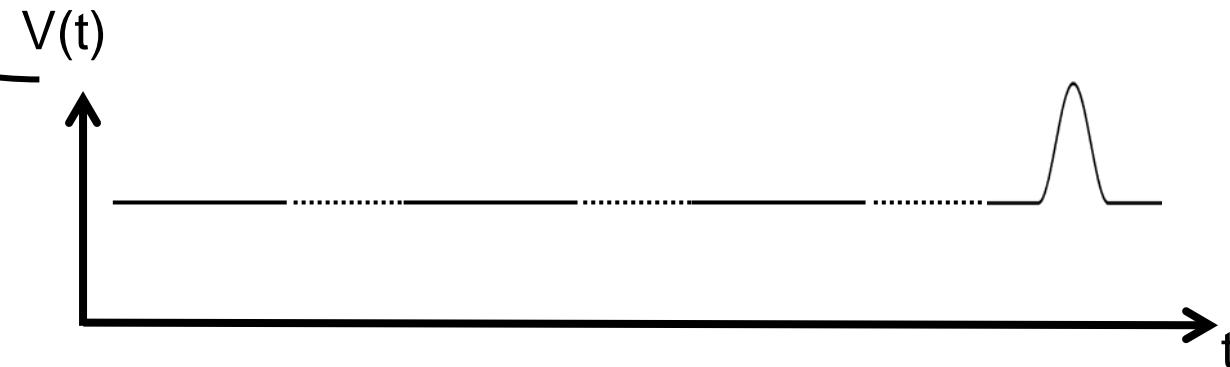
Pump and reset of drain node



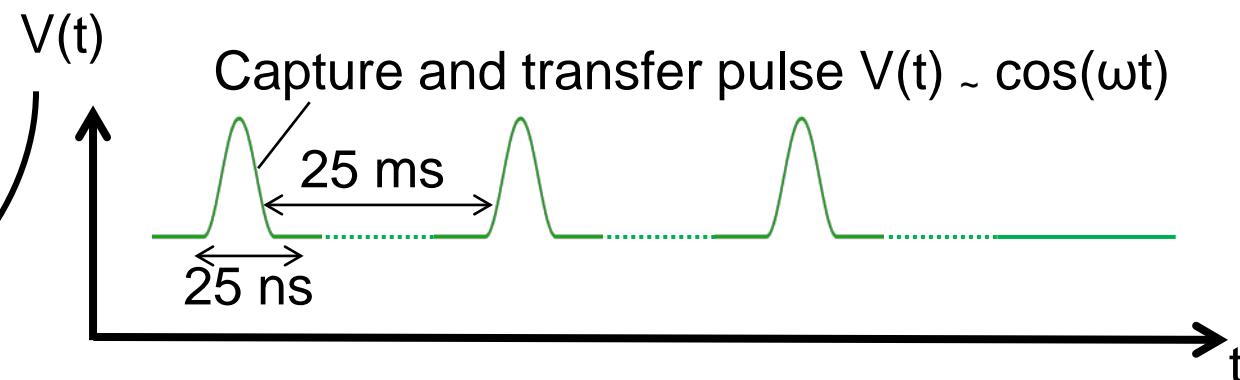
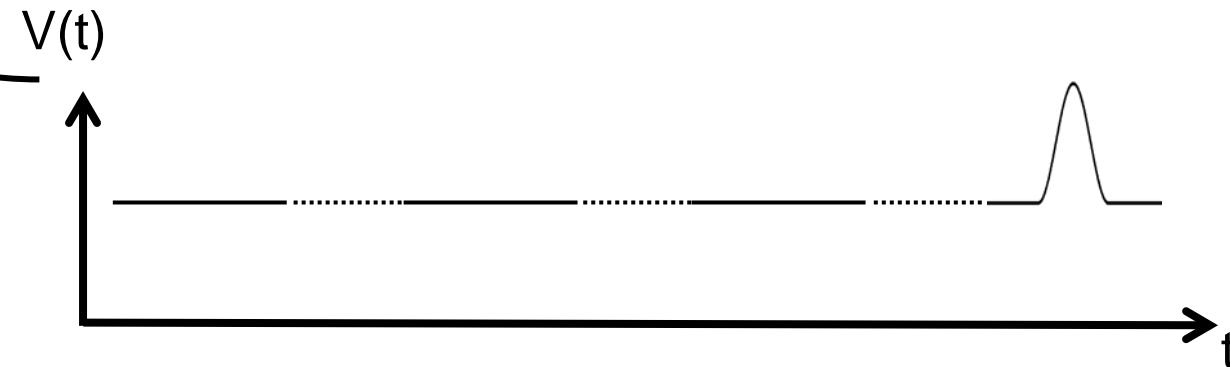
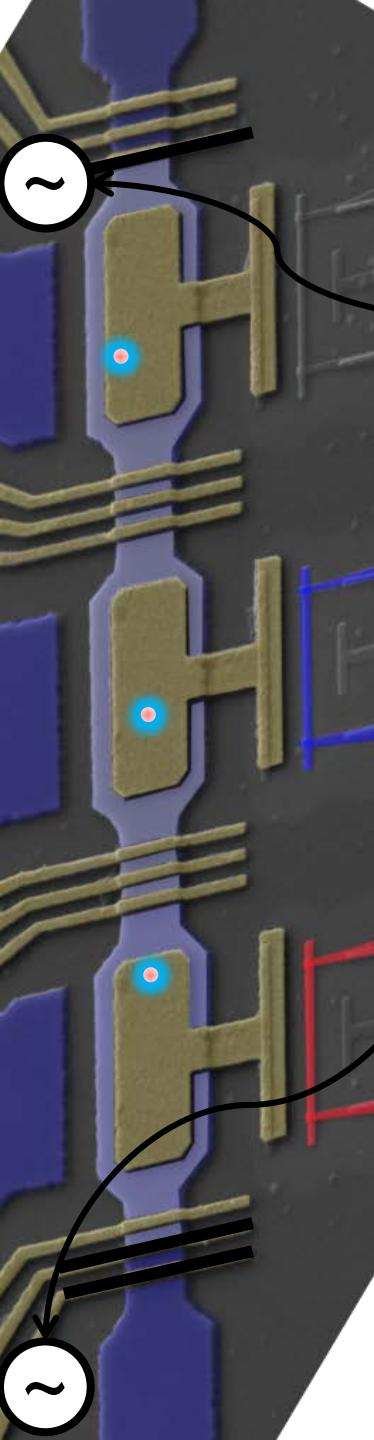
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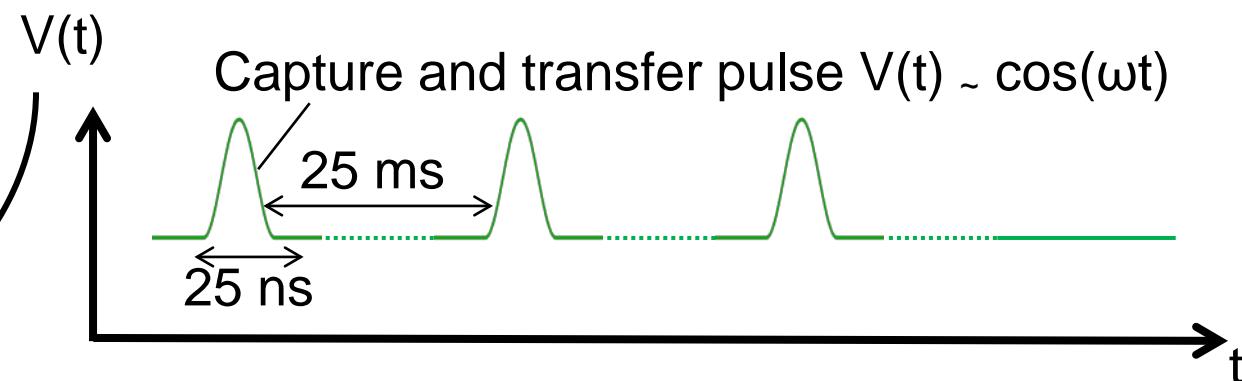
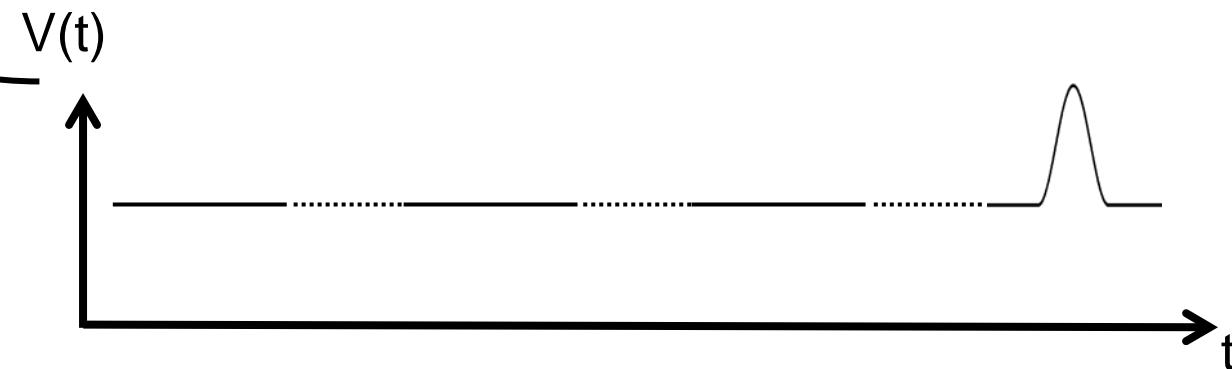
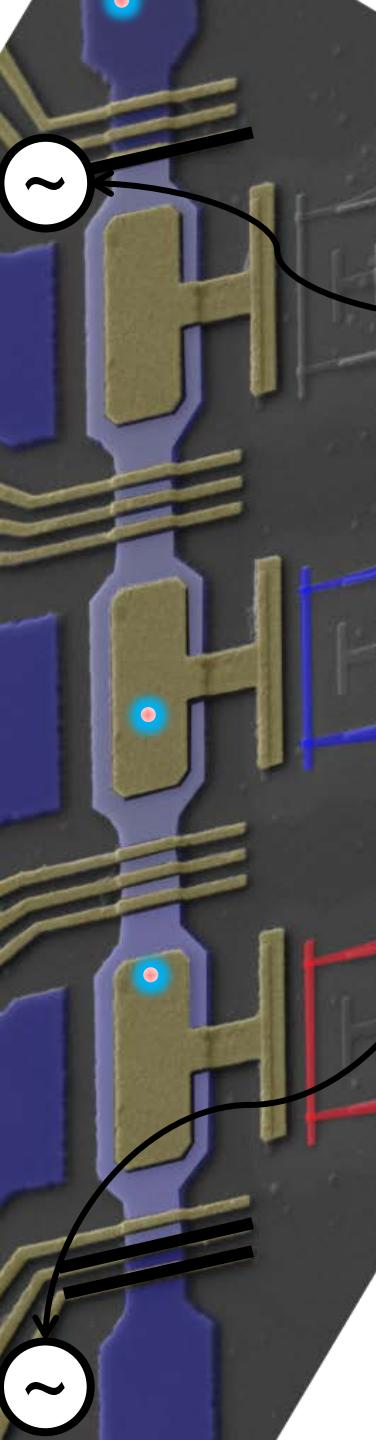
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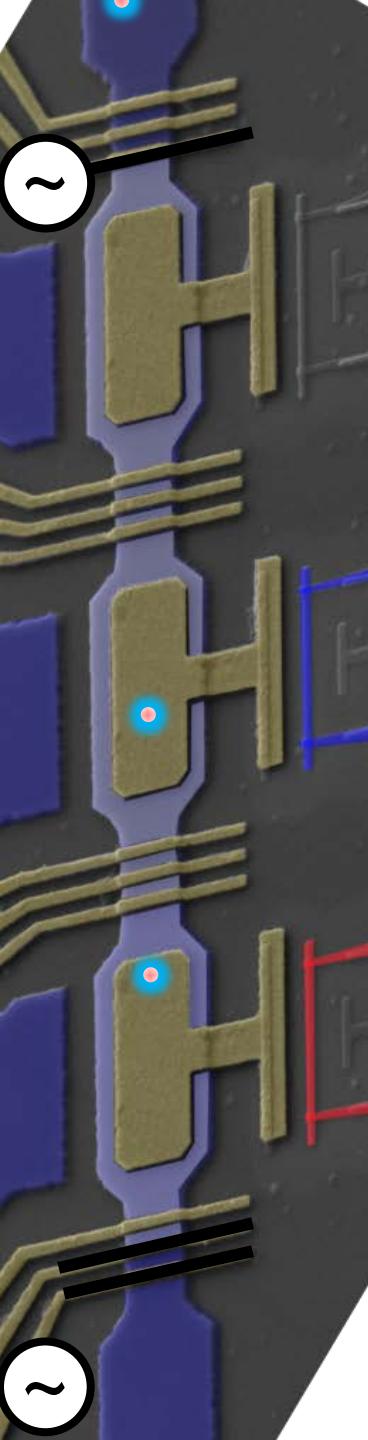


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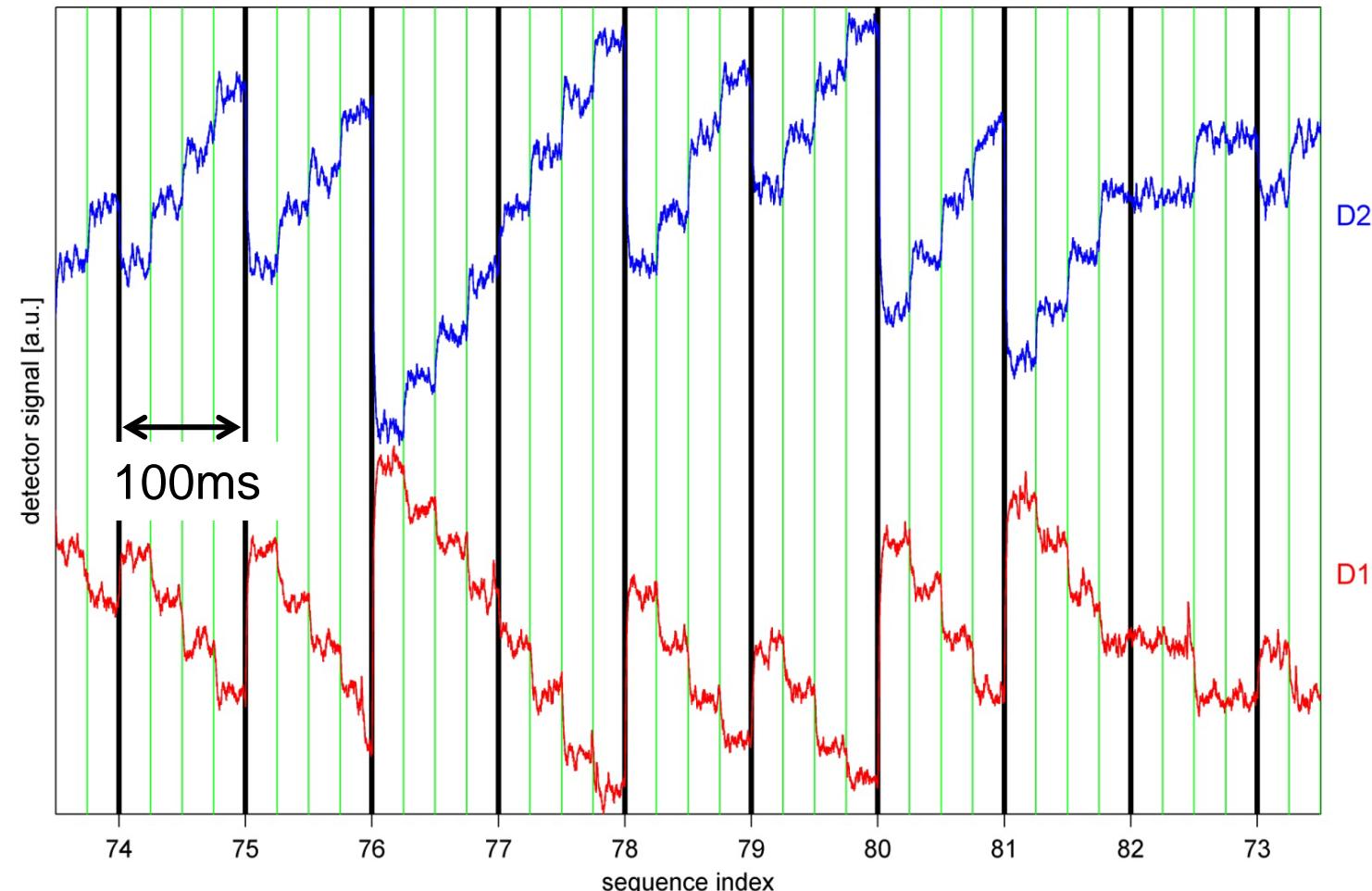
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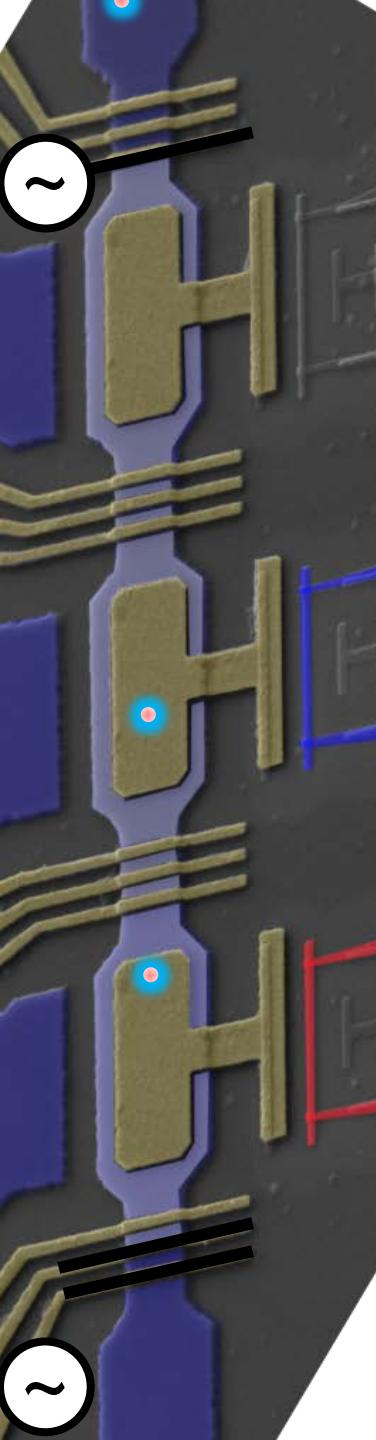




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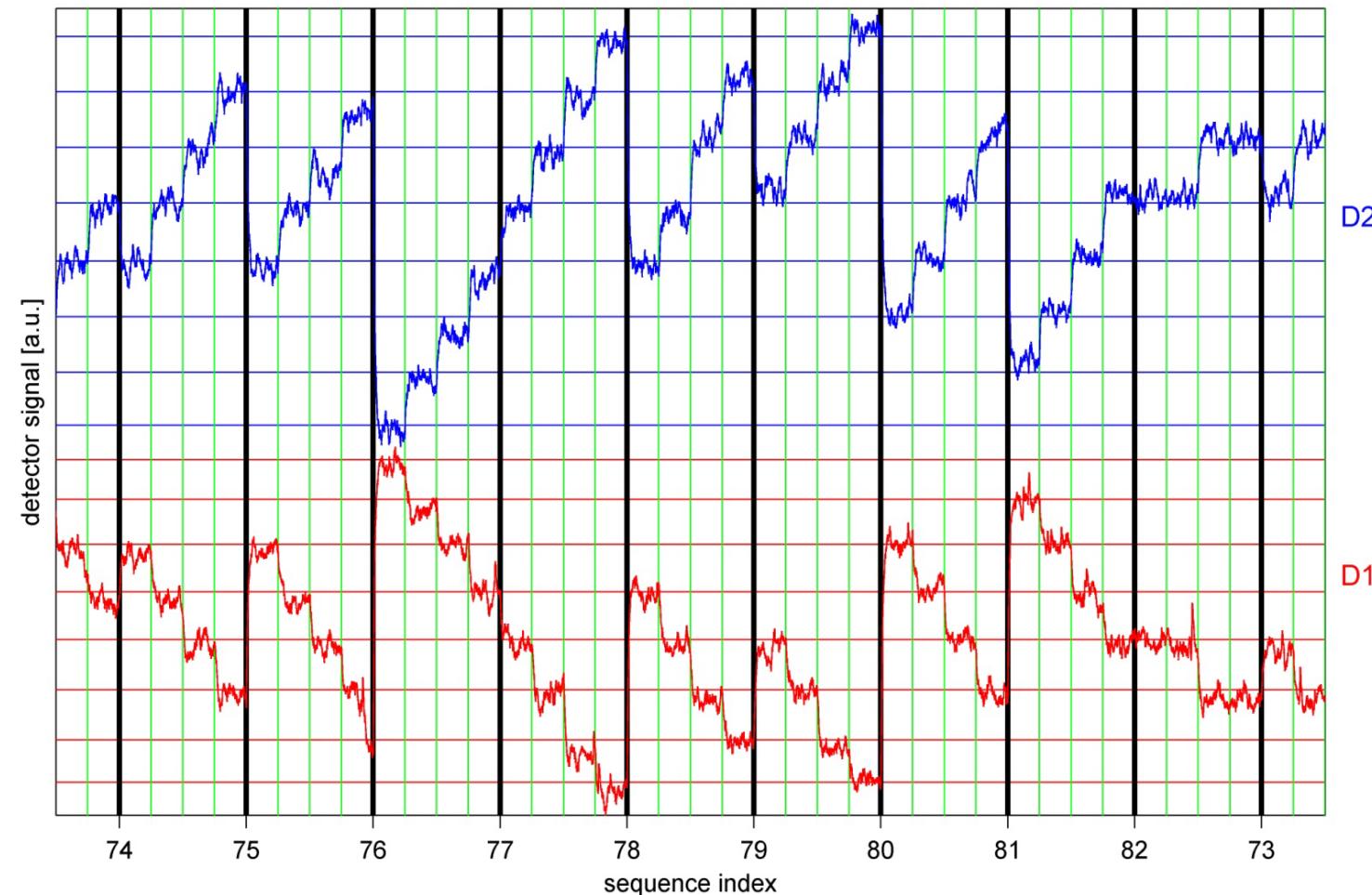
PTB



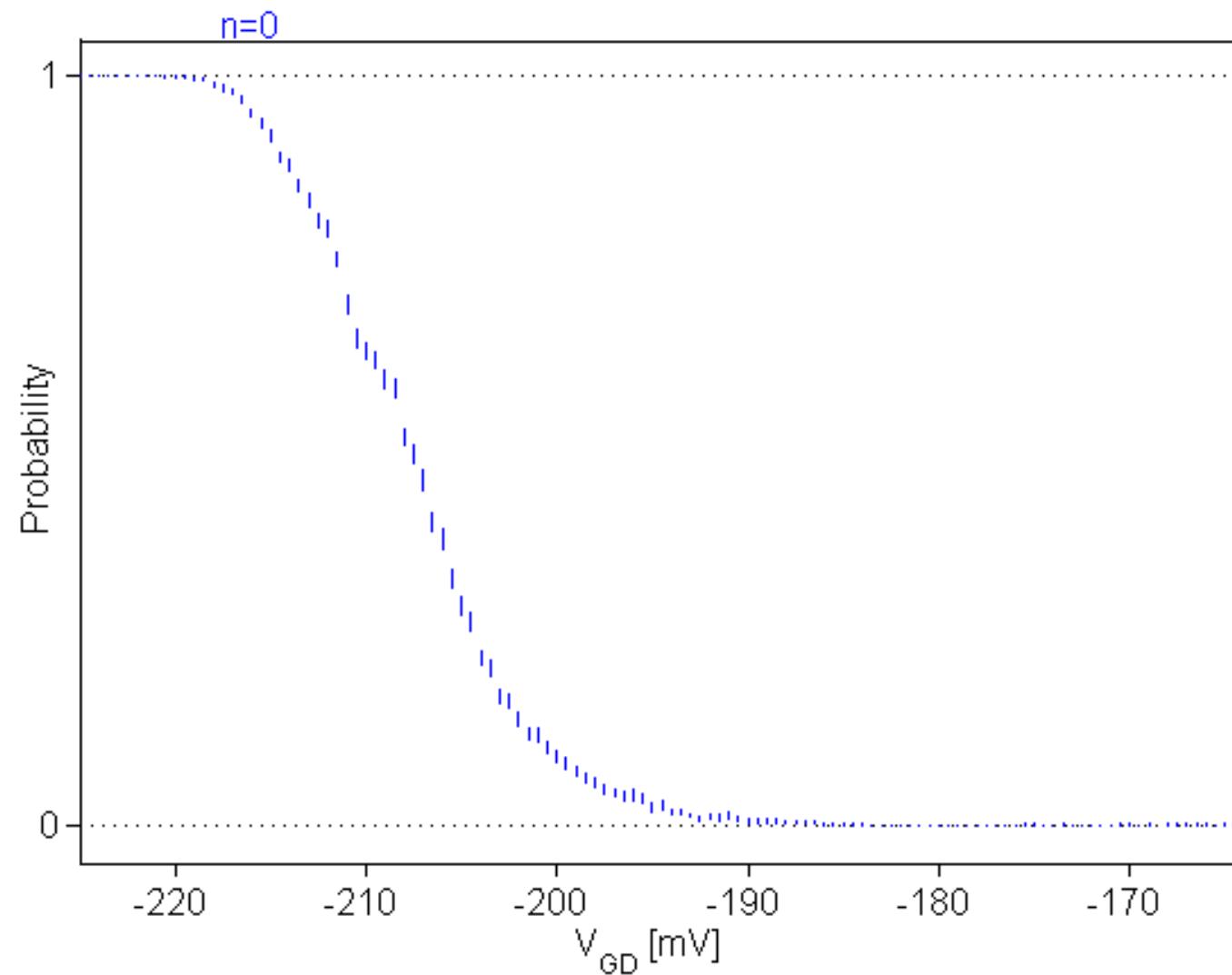


Pump and reset of drain node

PTB



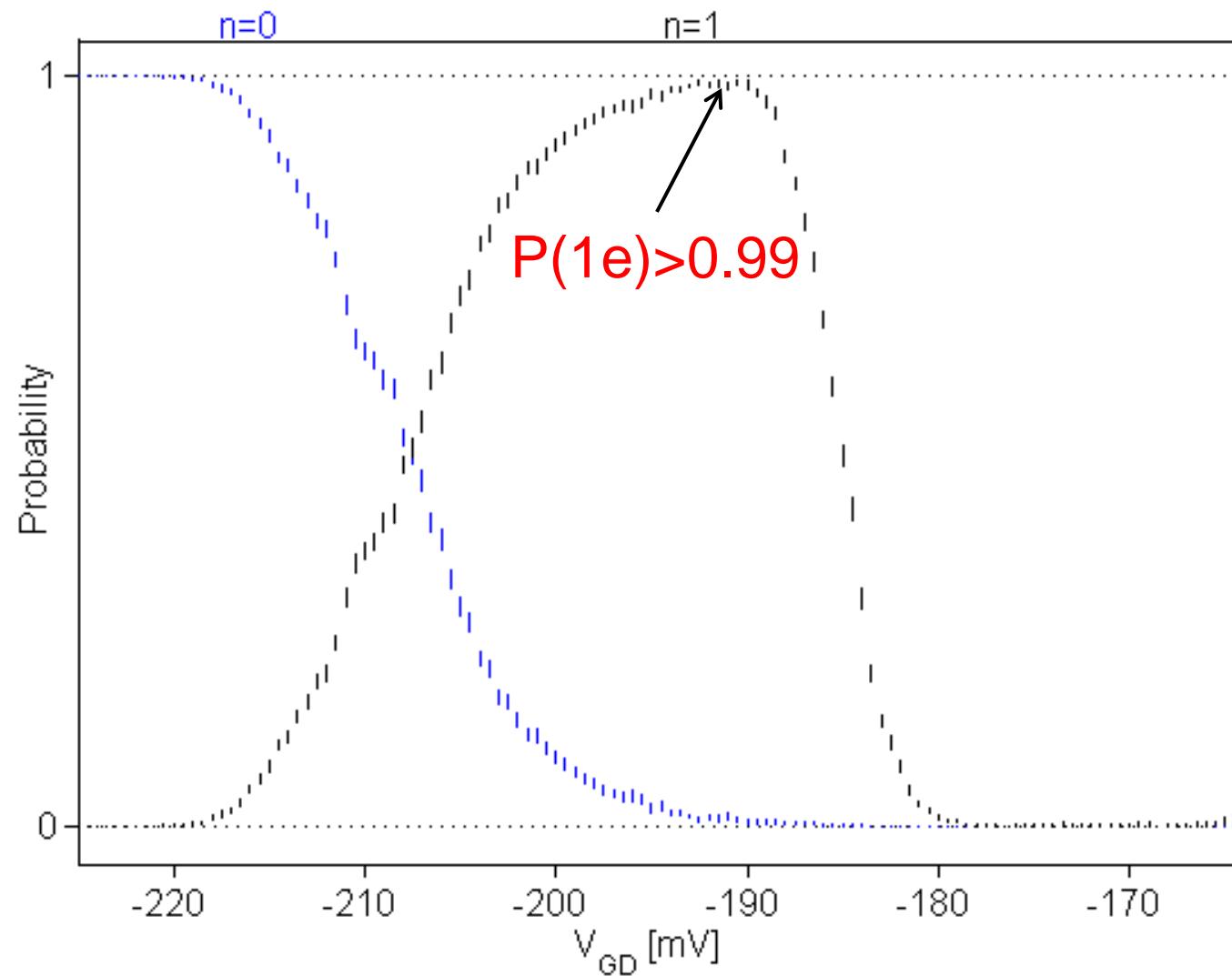
Capture probability



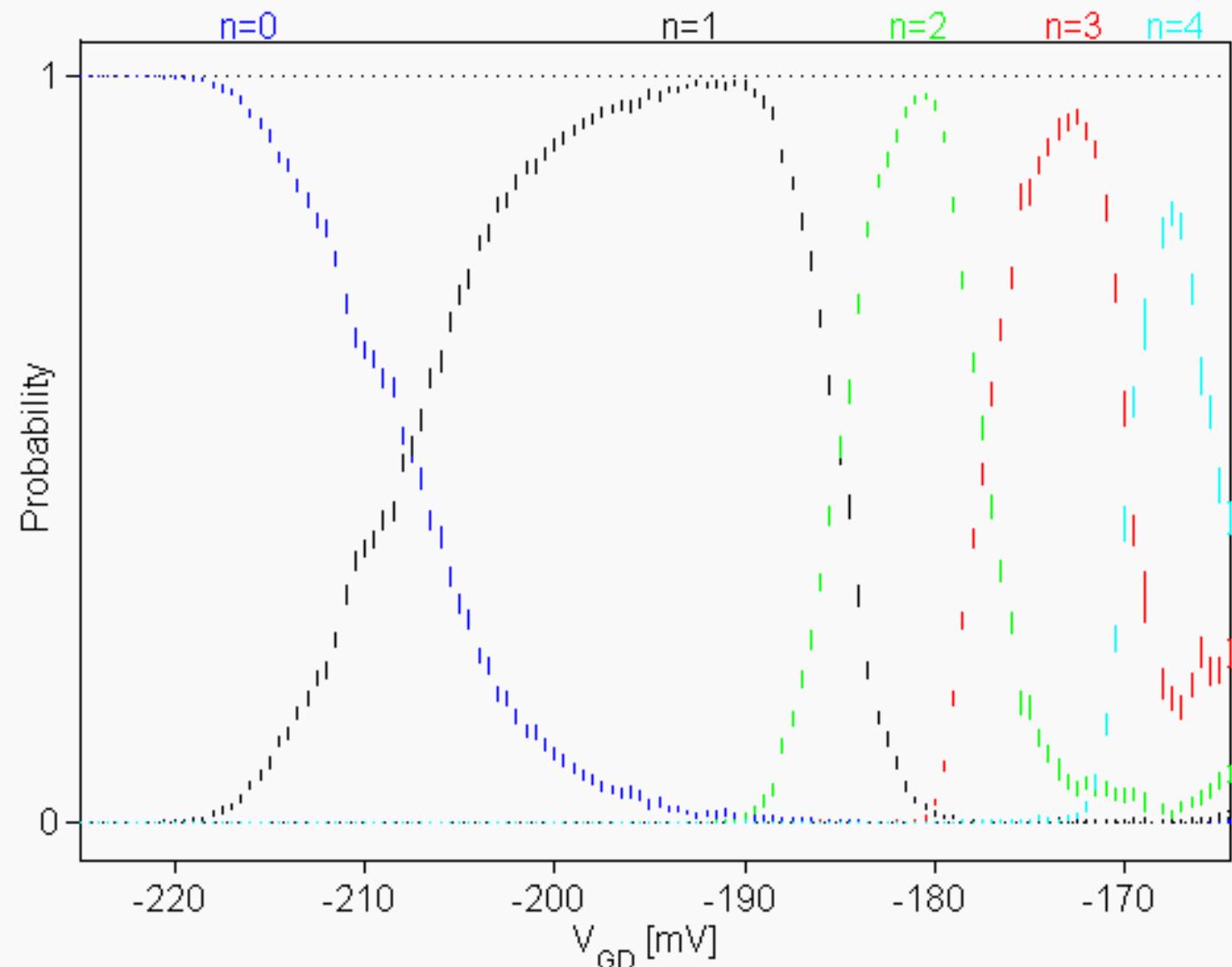


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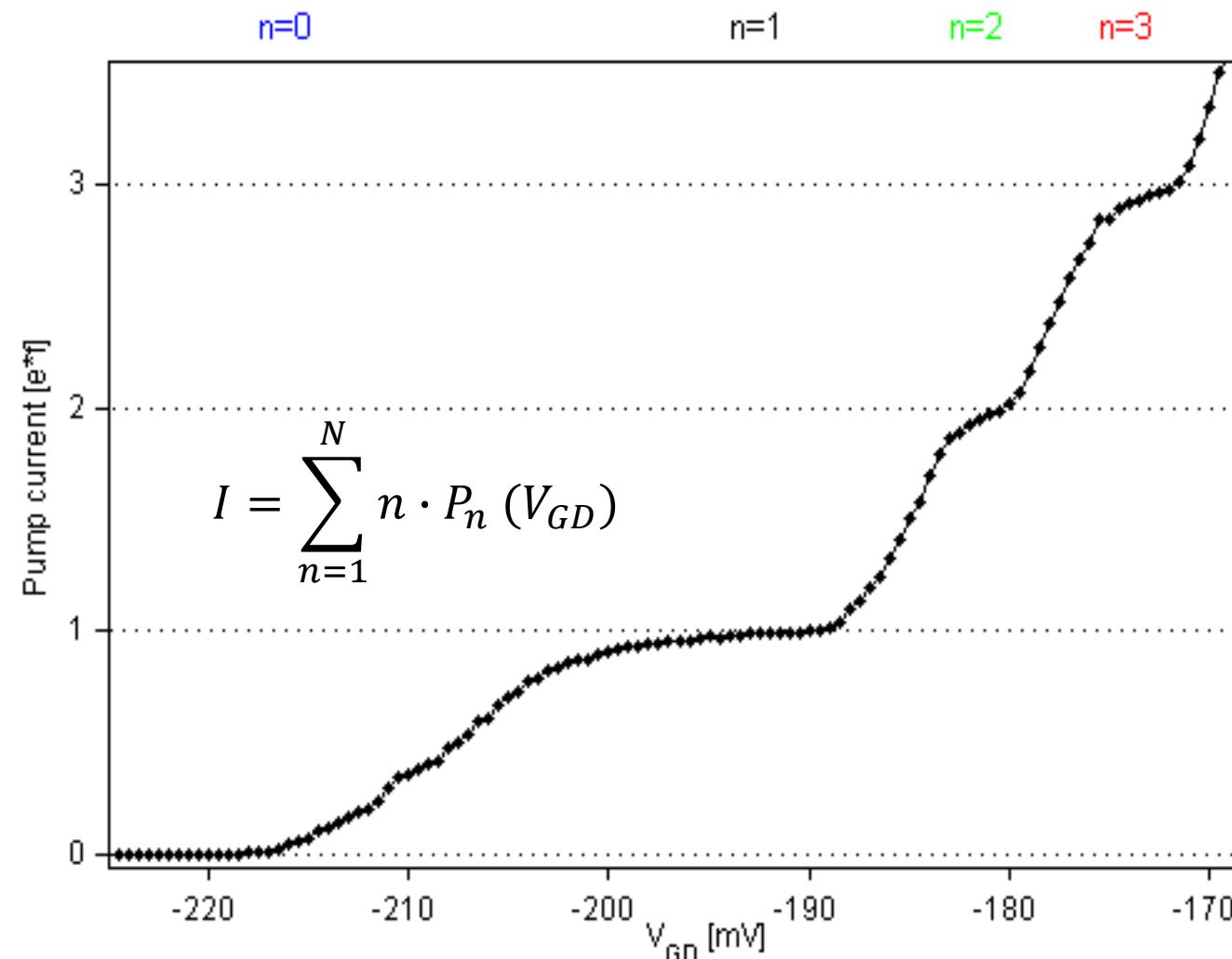
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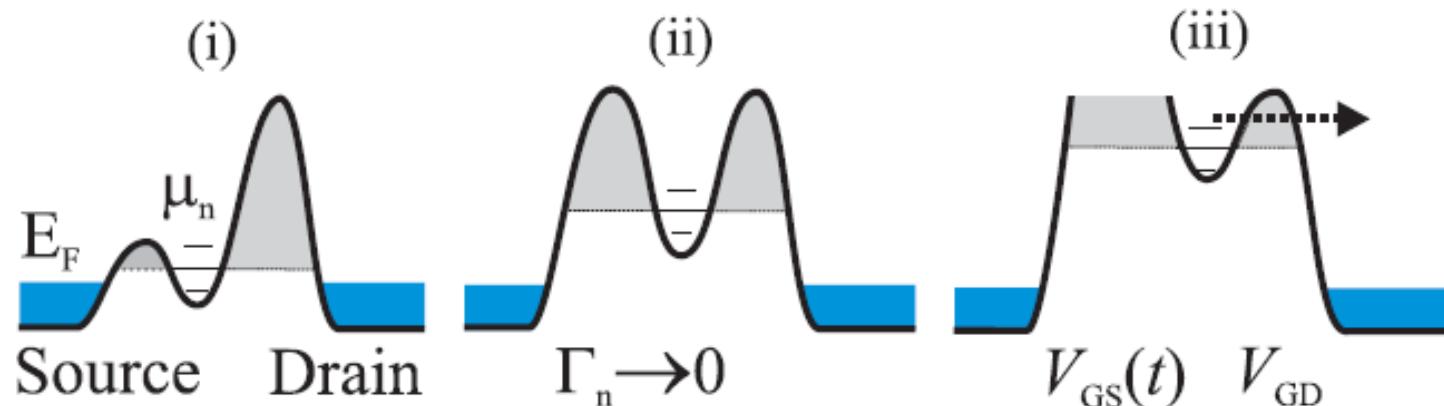
Capture probabilities



Calculated current



Model calculation



Time-dependent potential on left gate affects

- Barrier between source and dot (Tunneling rate Γ_n)
- Chemical potential of the dot μ_n

Thermal model

- Population of the dot follows adiabatically the lead's thermal distribution
- Then sudden decoupling freezes the states of the dot

Decay cascade model

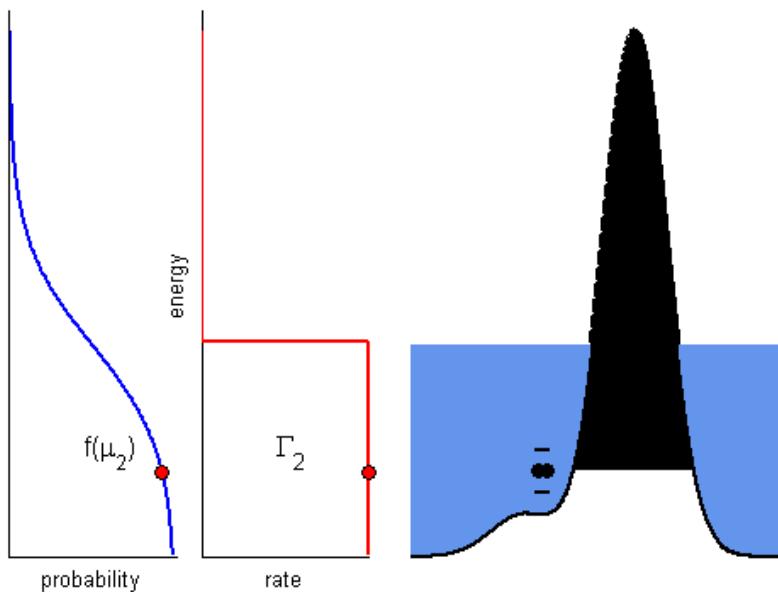
- At low temperatures, $f(\mu_n)$ may go to zero much faster than Γ_n
- Gradual decoupling limit

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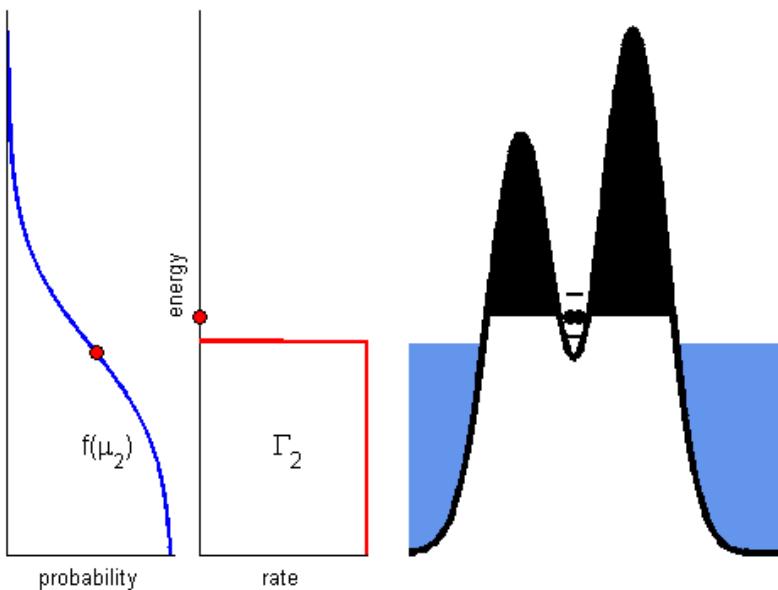
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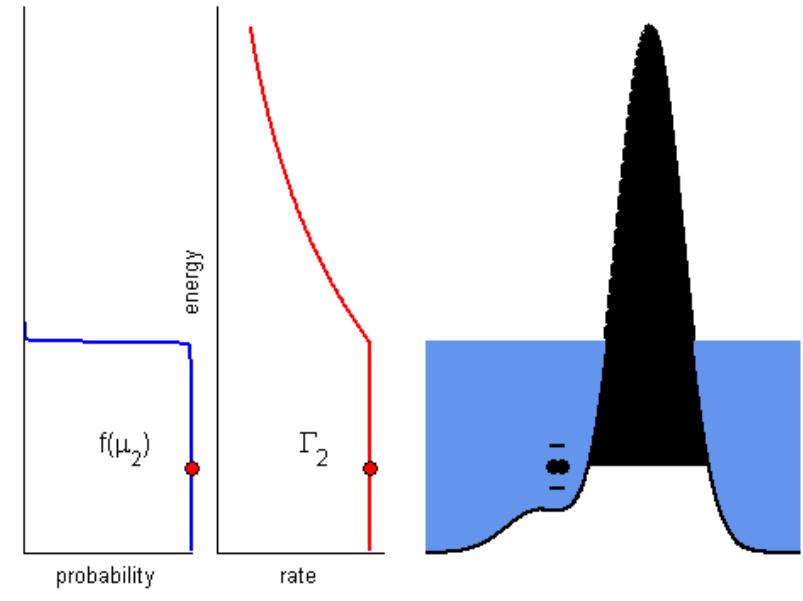
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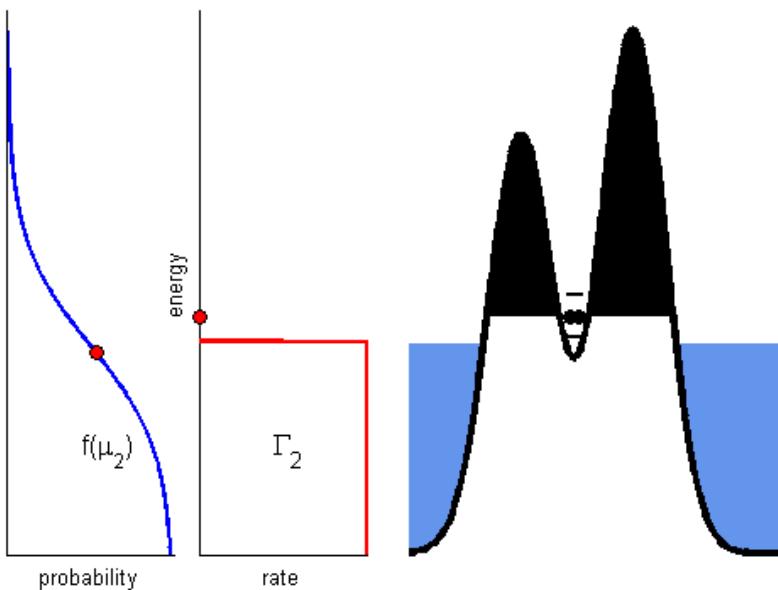
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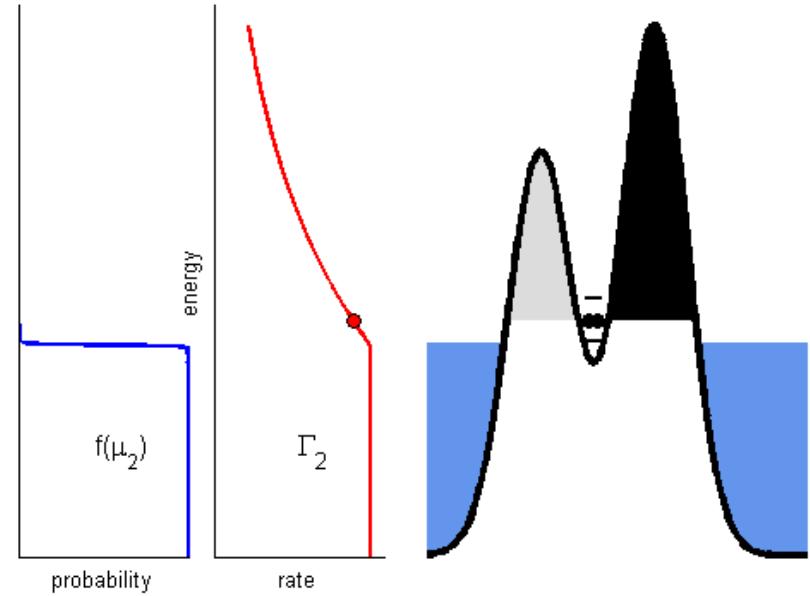
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$$P_n = (1 - f[\mu_{n+1}(t_{n+1}^c)]) \prod_{m=1}^n f[\mu_m(t_m^c)]$$

$$f(\mu_n) \equiv \frac{1}{1 + e^{(\mu_n - \mu)/k_B T}}$$

$$P_n = e^{-X_n} \prod_{j=n+1}^N (1 - e^{-X_j})$$

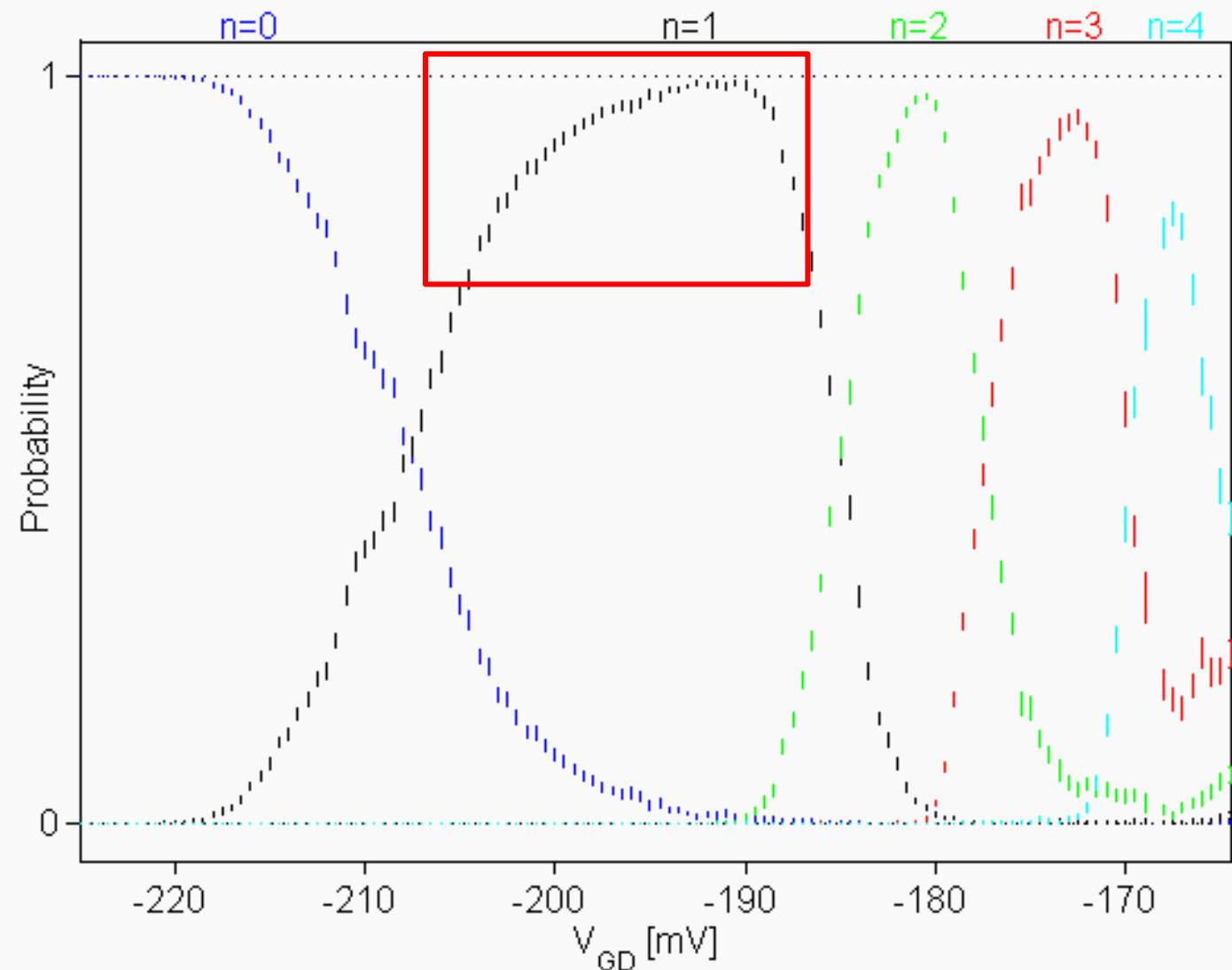
$$X_n \equiv \int_{t_b}^{\infty} \Gamma_n(t') dt'$$

Ansatz:

$$\begin{aligned} \mu_m(t_m^c)/k_B T &= -\alpha_{\mu,n} V_{\text{GD}} + \Delta_{\mu,n} \\ \ln X_n &= -\alpha_{X,n} V_{\text{GD}} + \Delta_{X,n} \end{aligned}$$



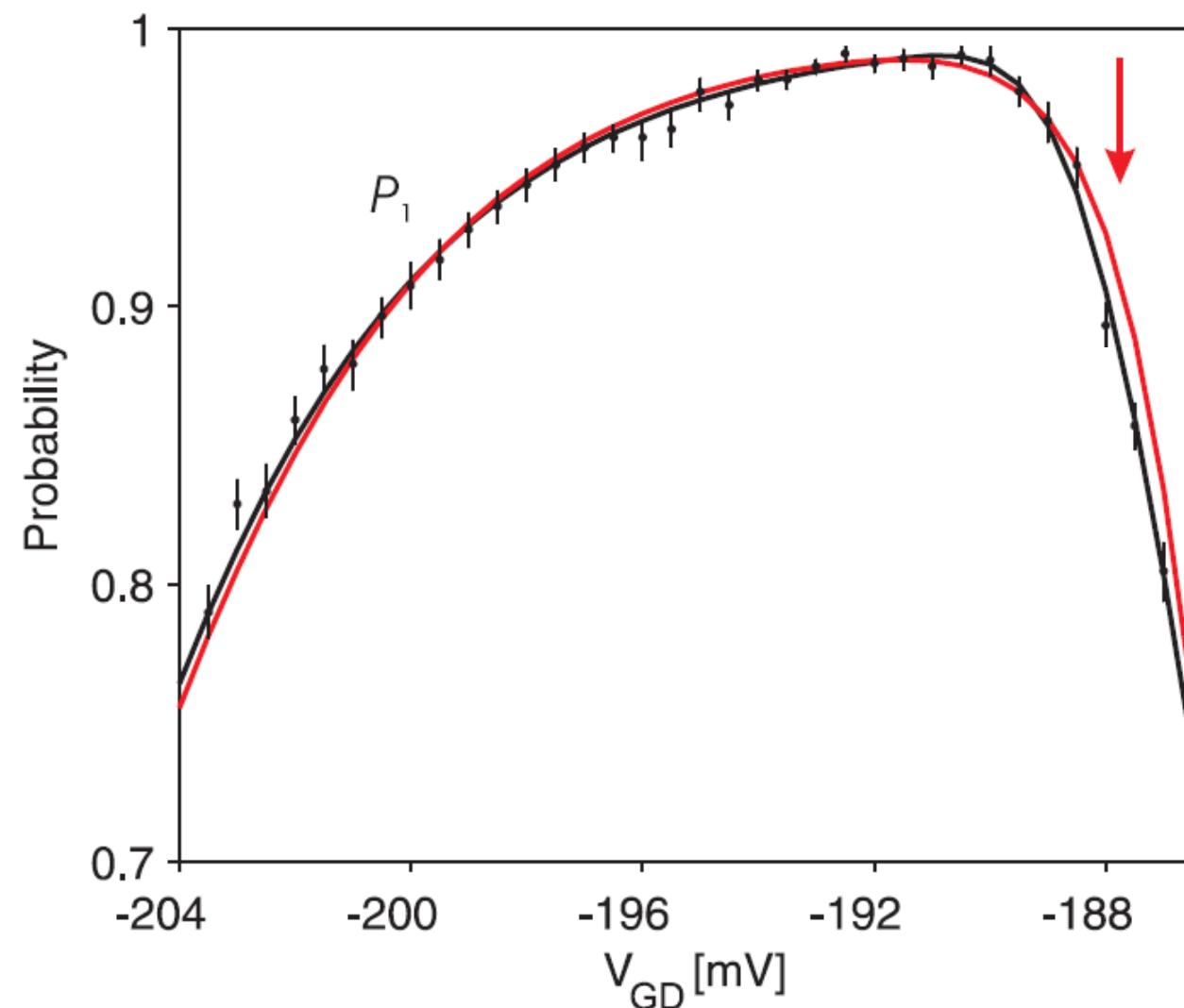
Capture probabilities





Model fits

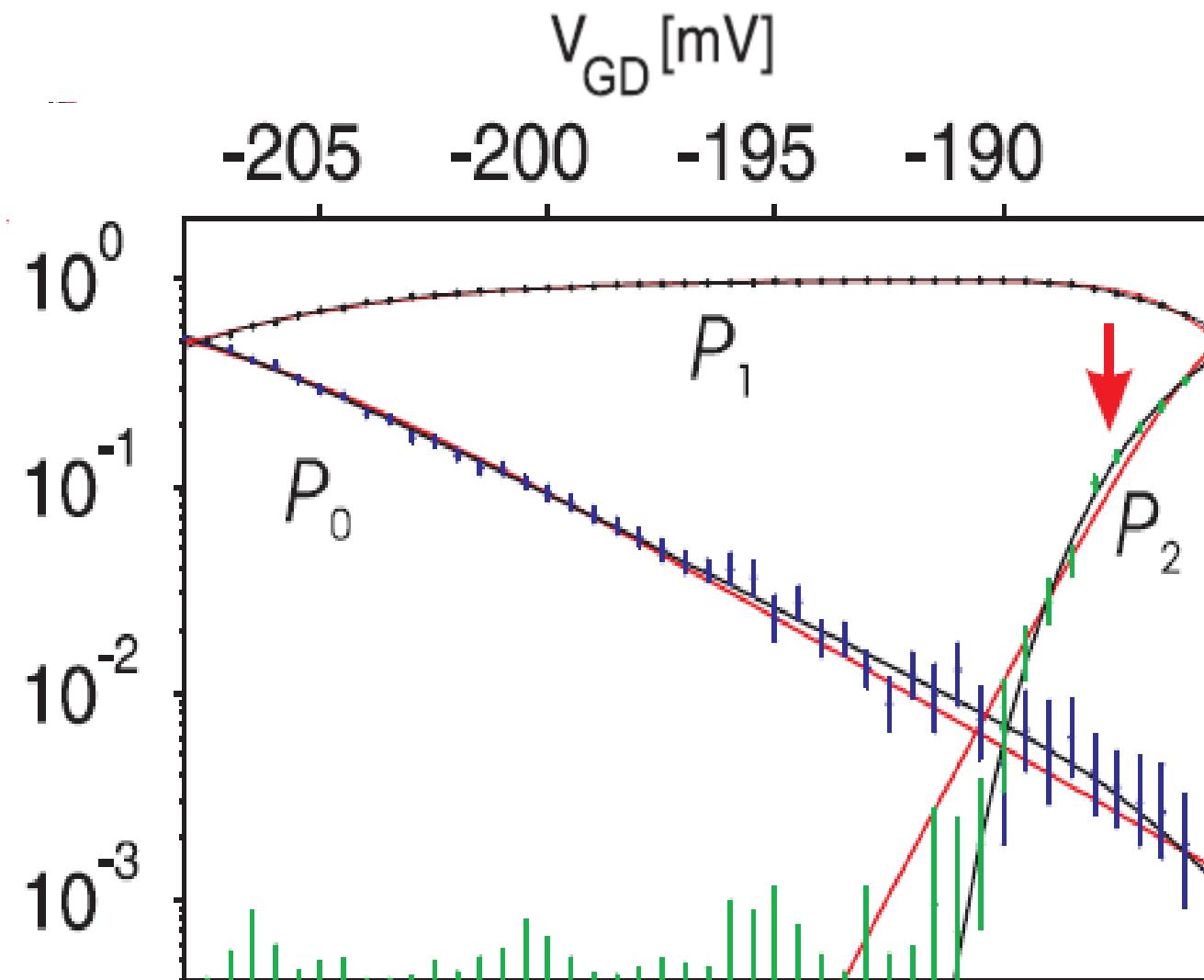
PTB





Model fits

PTB





Optimization strategies

Thermal model

Pump fidelity may profit from further lowering of temperature

Reduced coupling between barrier and plunger necessary

May be achieved by applying compensation pulses onto the 2nd gate

Decay cascade model

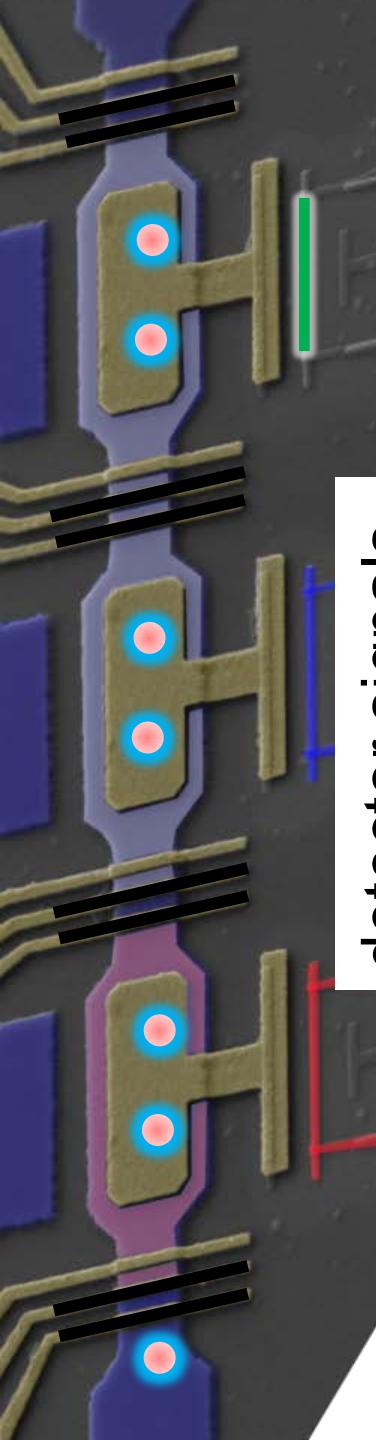
Lowering the temperature will not increase fidelity

Instead increase the separation of decay steps by

- Large ratio of tunneling rates
- Large energy separation for different n

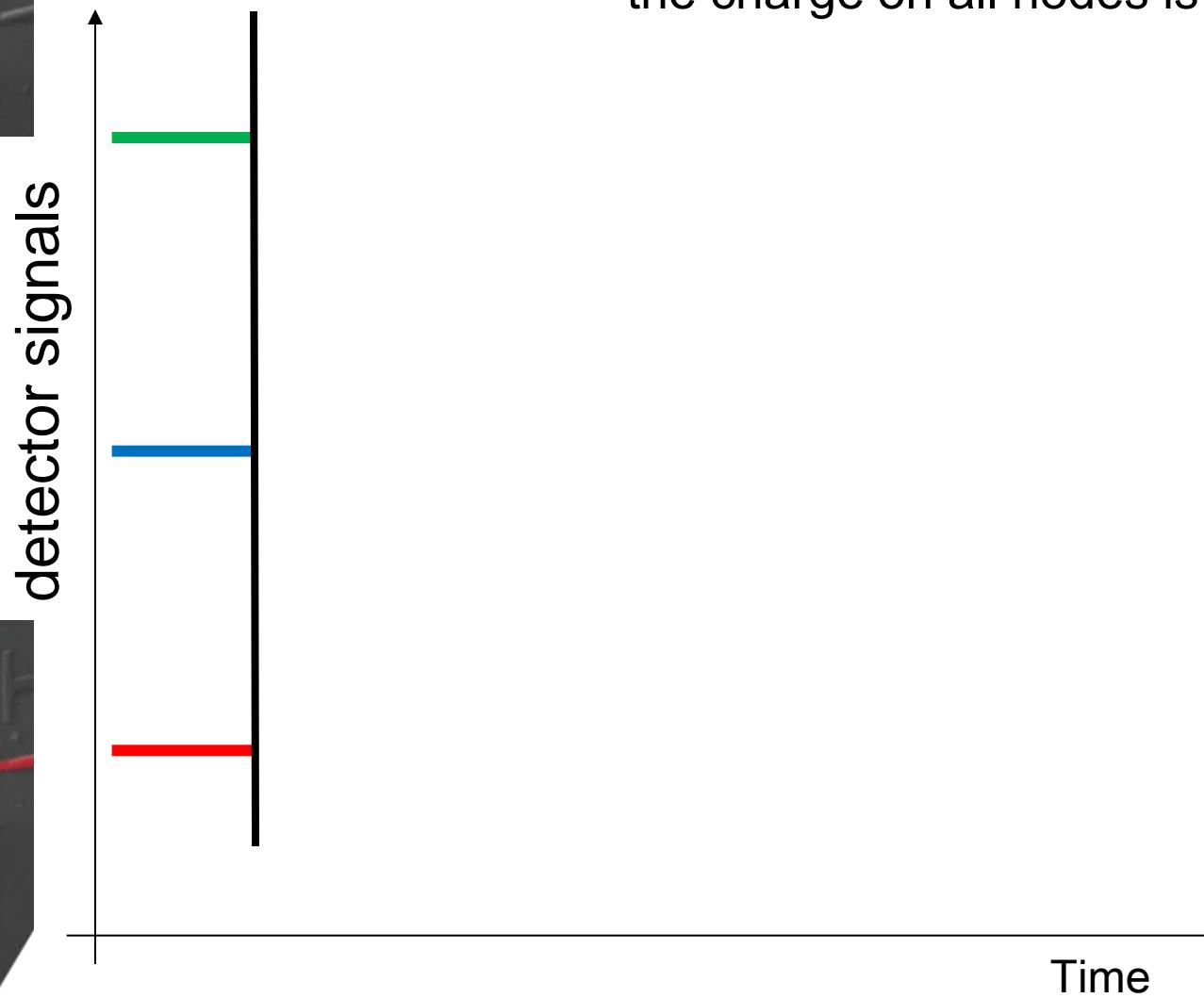
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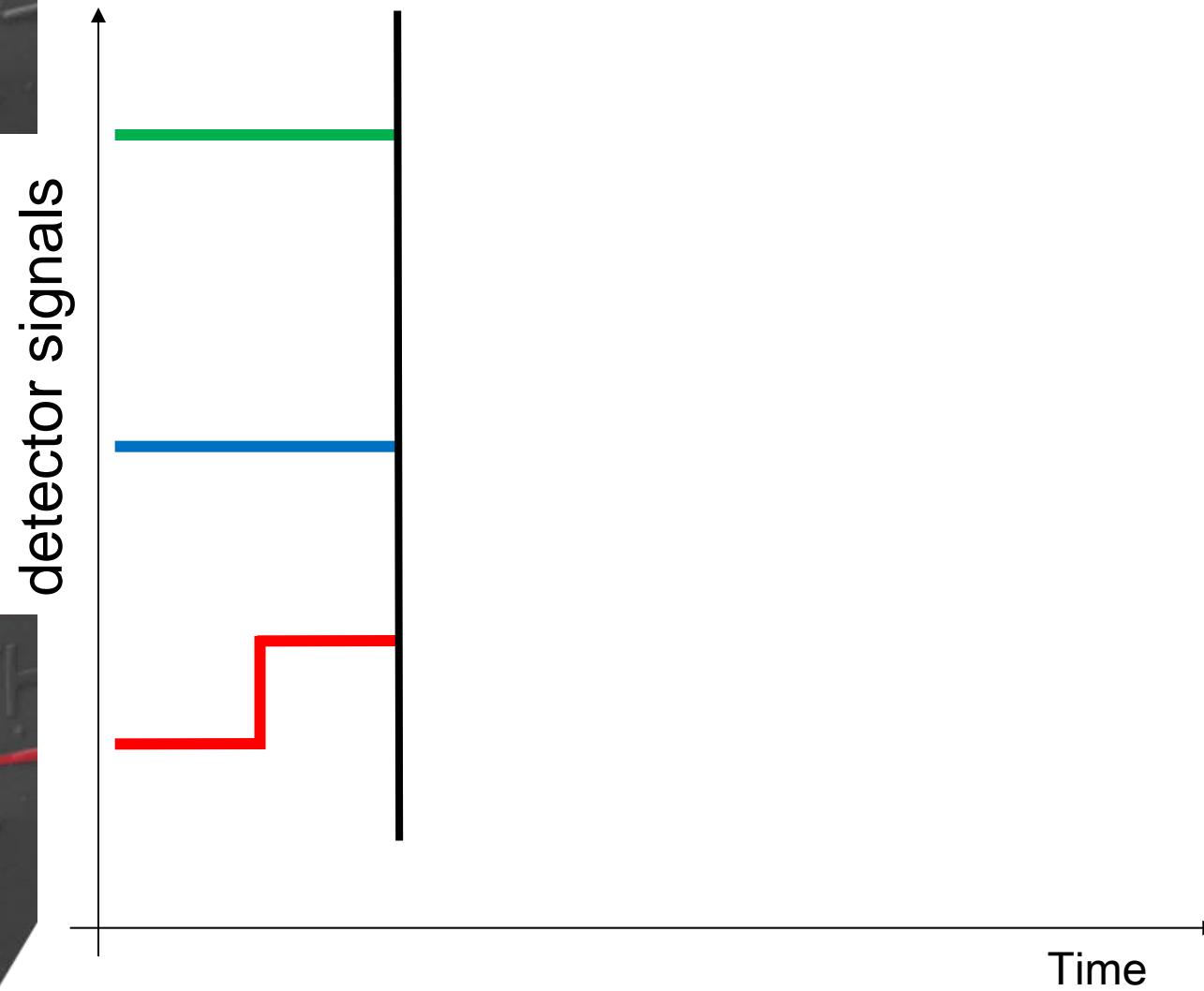
No errors: Constant node signals

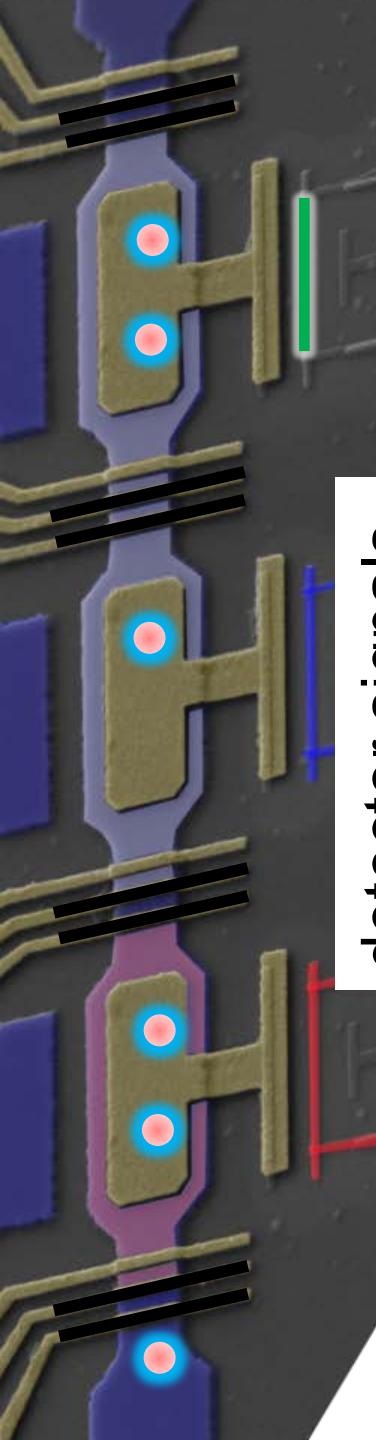
If all pumps work without errors,
the charge on all nodes is constant



Transfer error by first pump

Red detector monitors change in
the first island's charge state

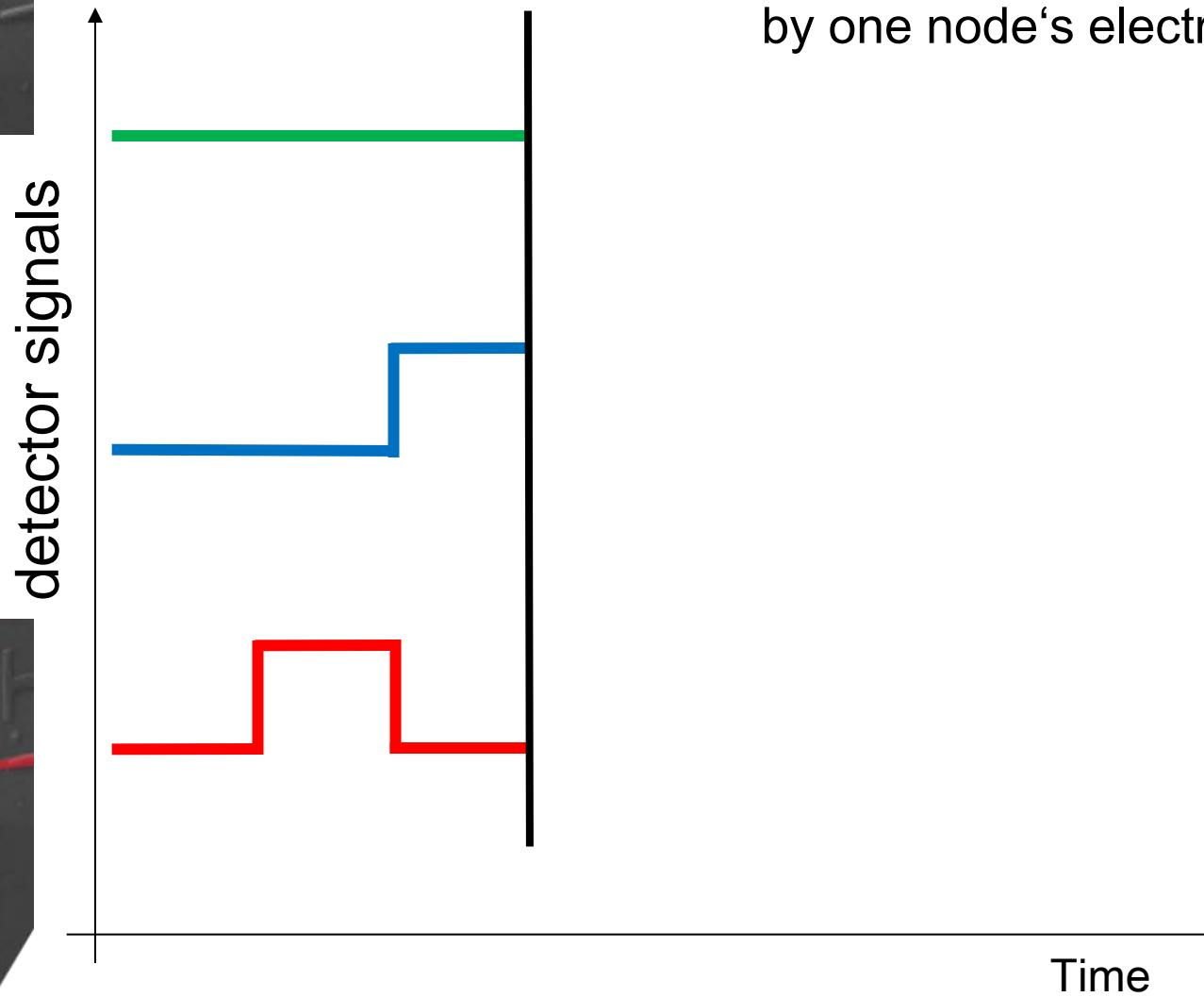


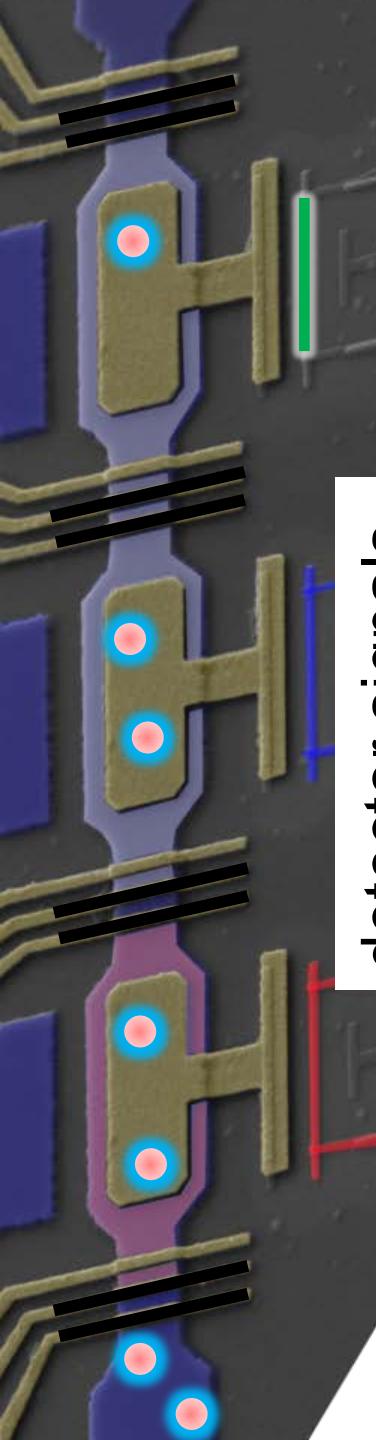


Consecutive error by second pump

PTB

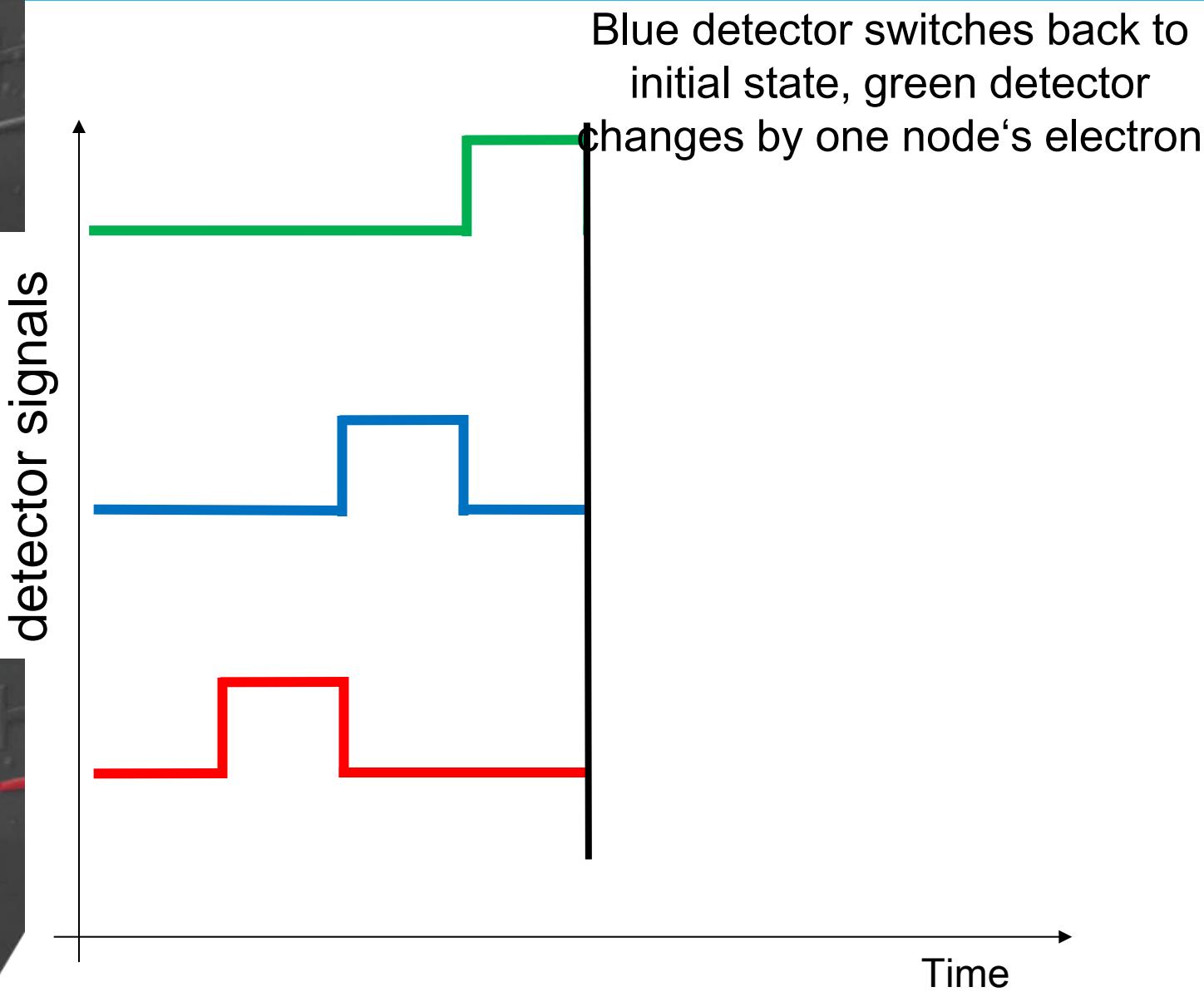
Red detector switches back to initial state, blue detector changes by one node's electron

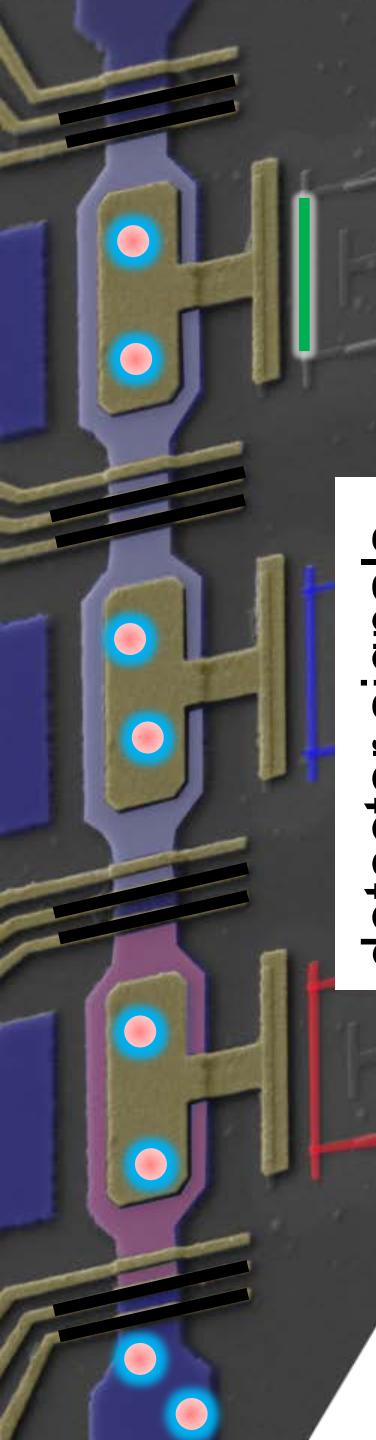




Consecutive error by third pump

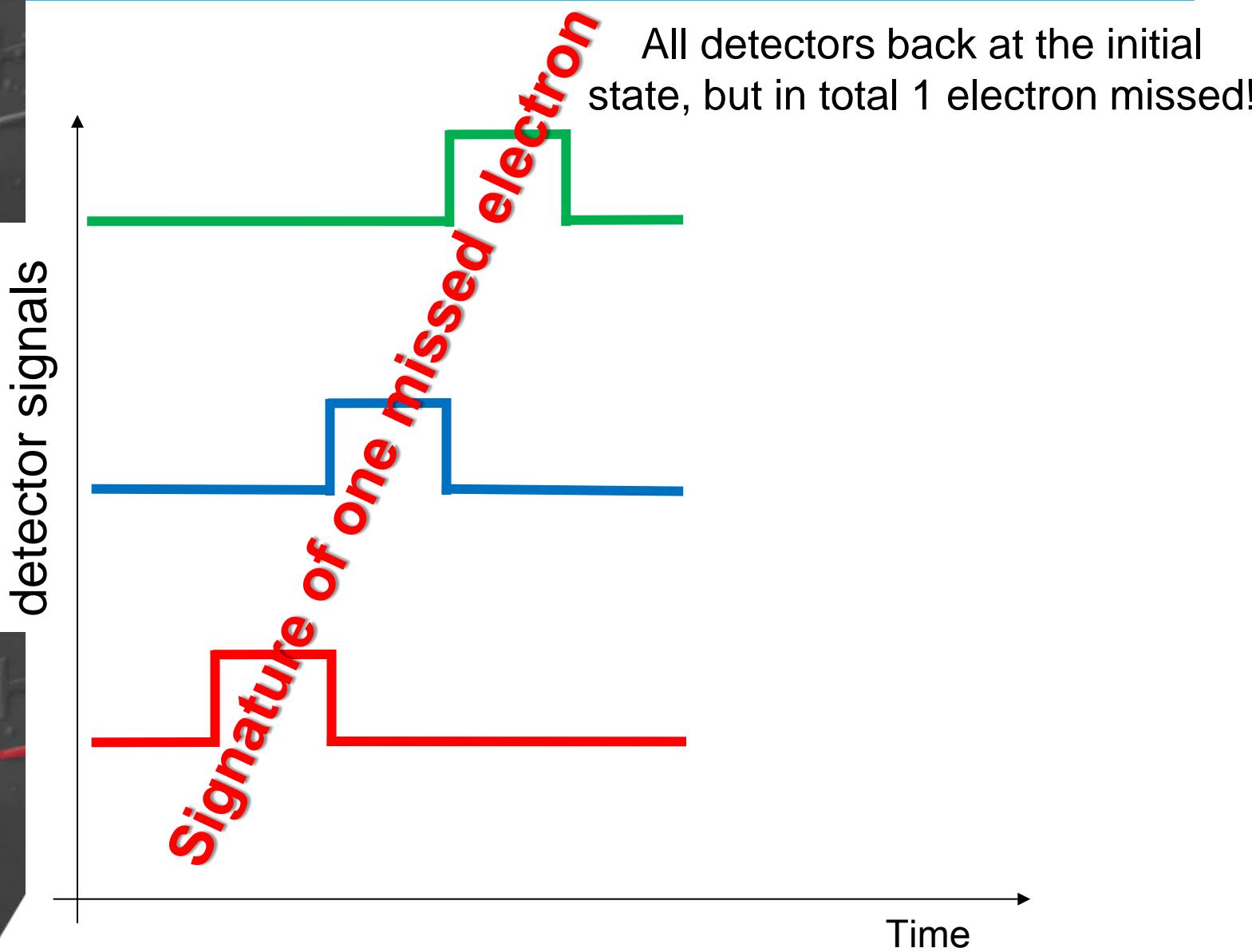
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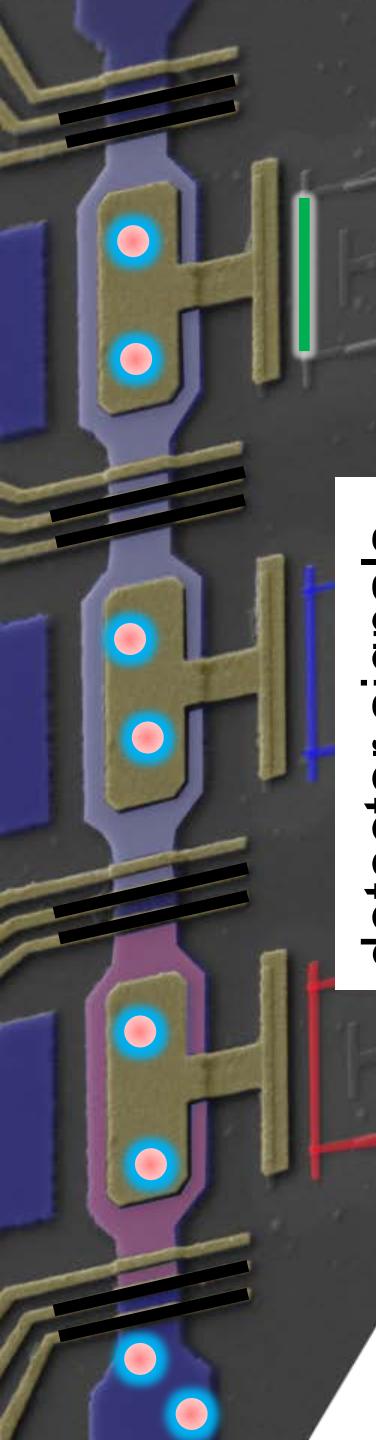




Consecutive error by fourth pump

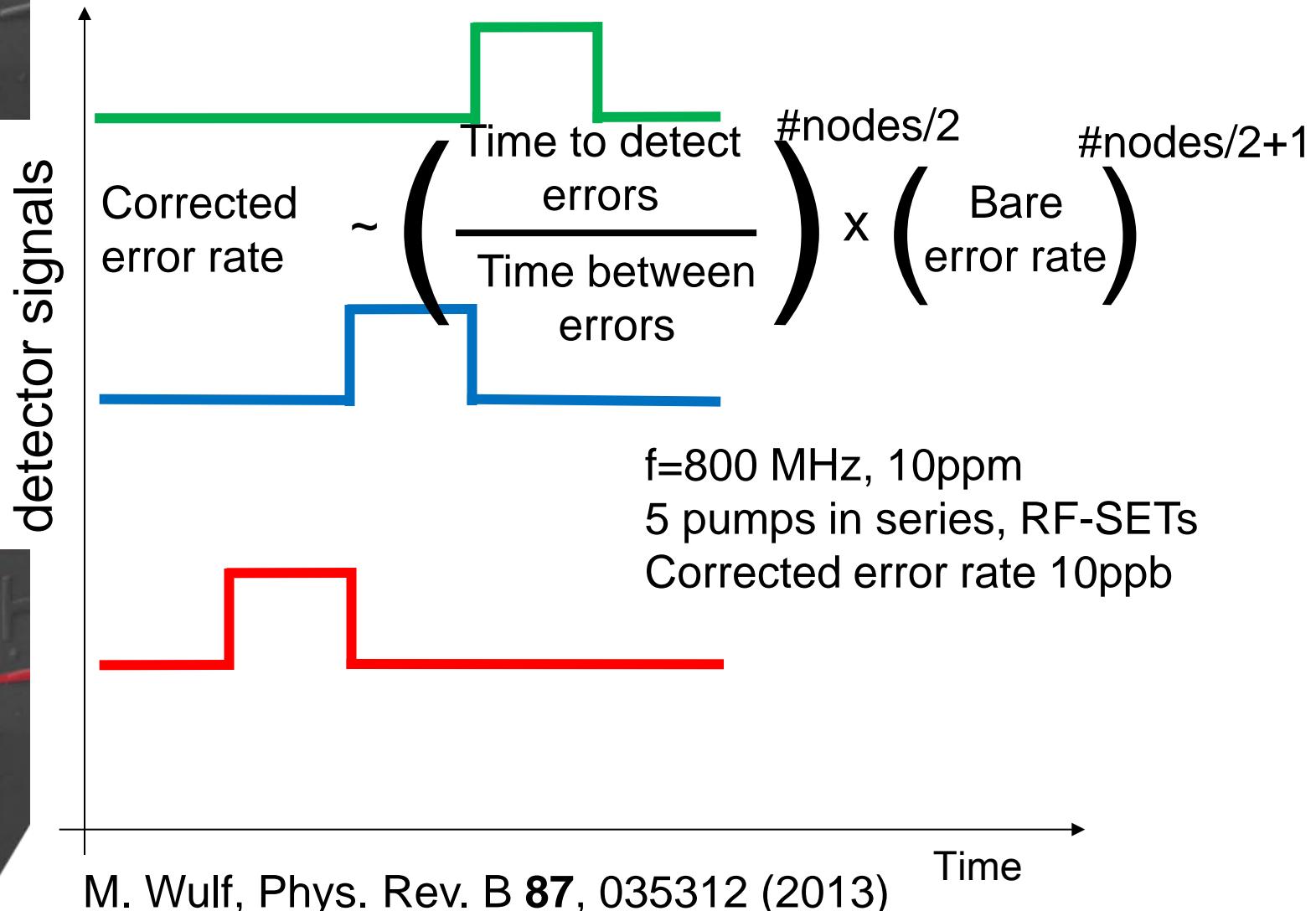
PTB





Consecutive error by fourth pump

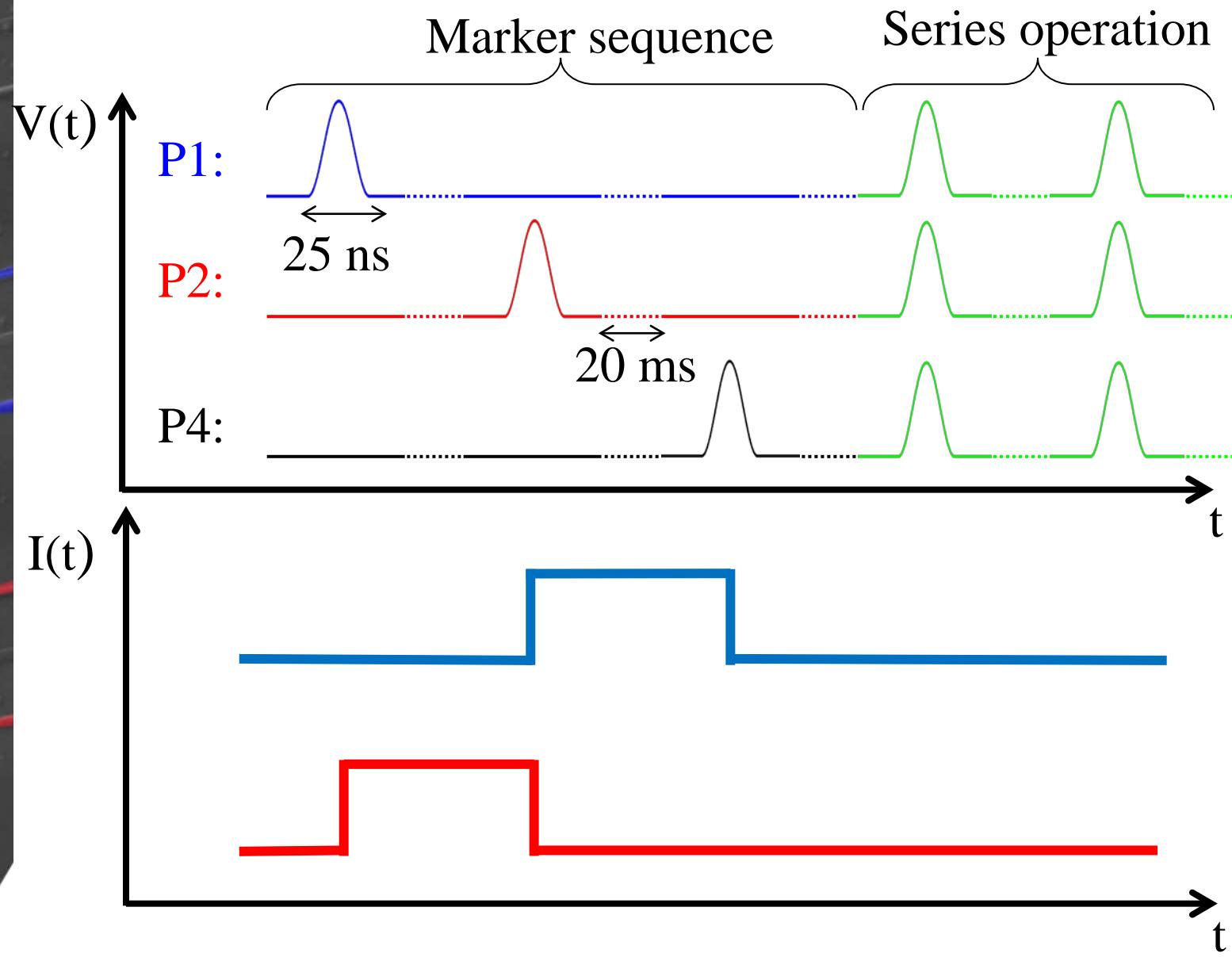
PTB





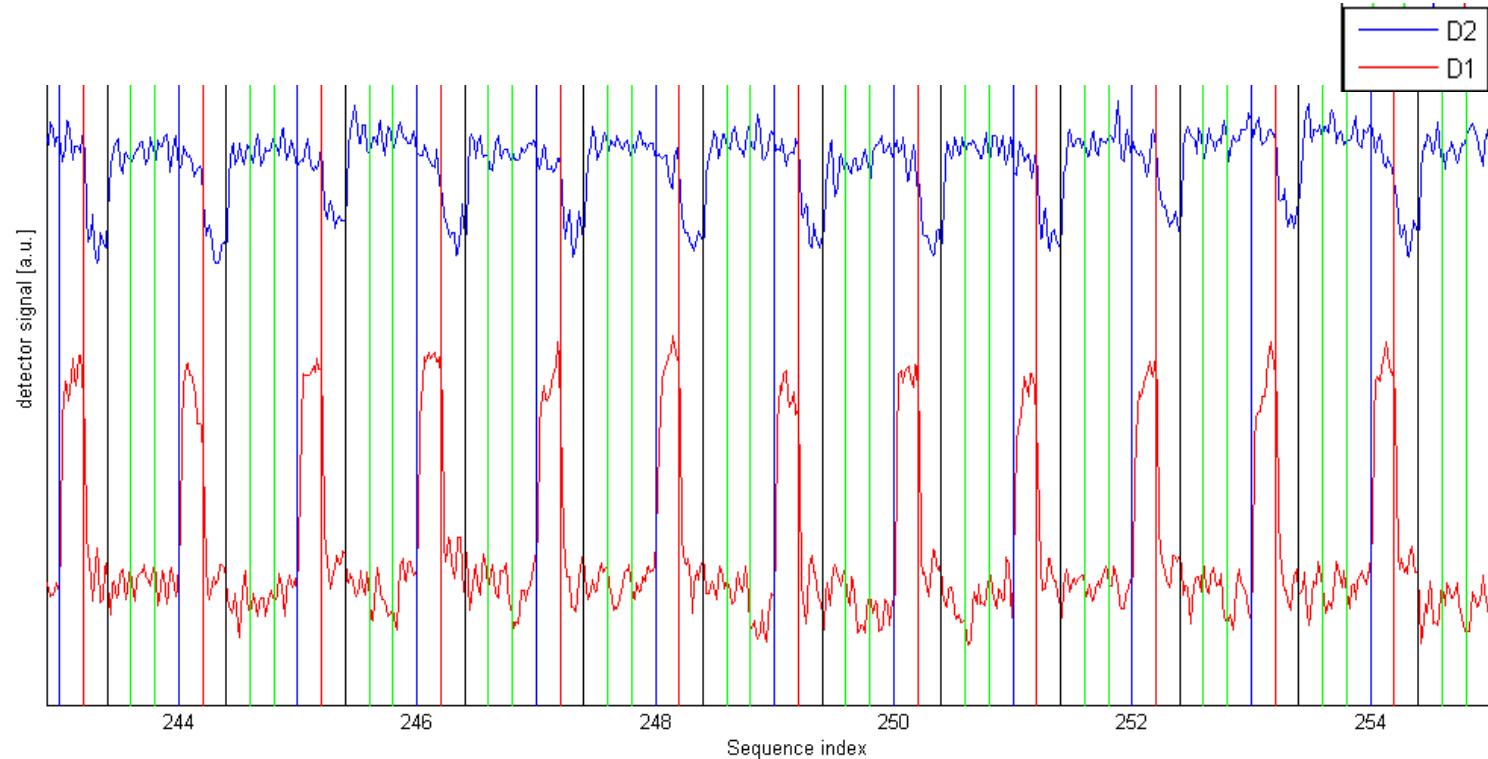
Simultaneous series pumping

PTB

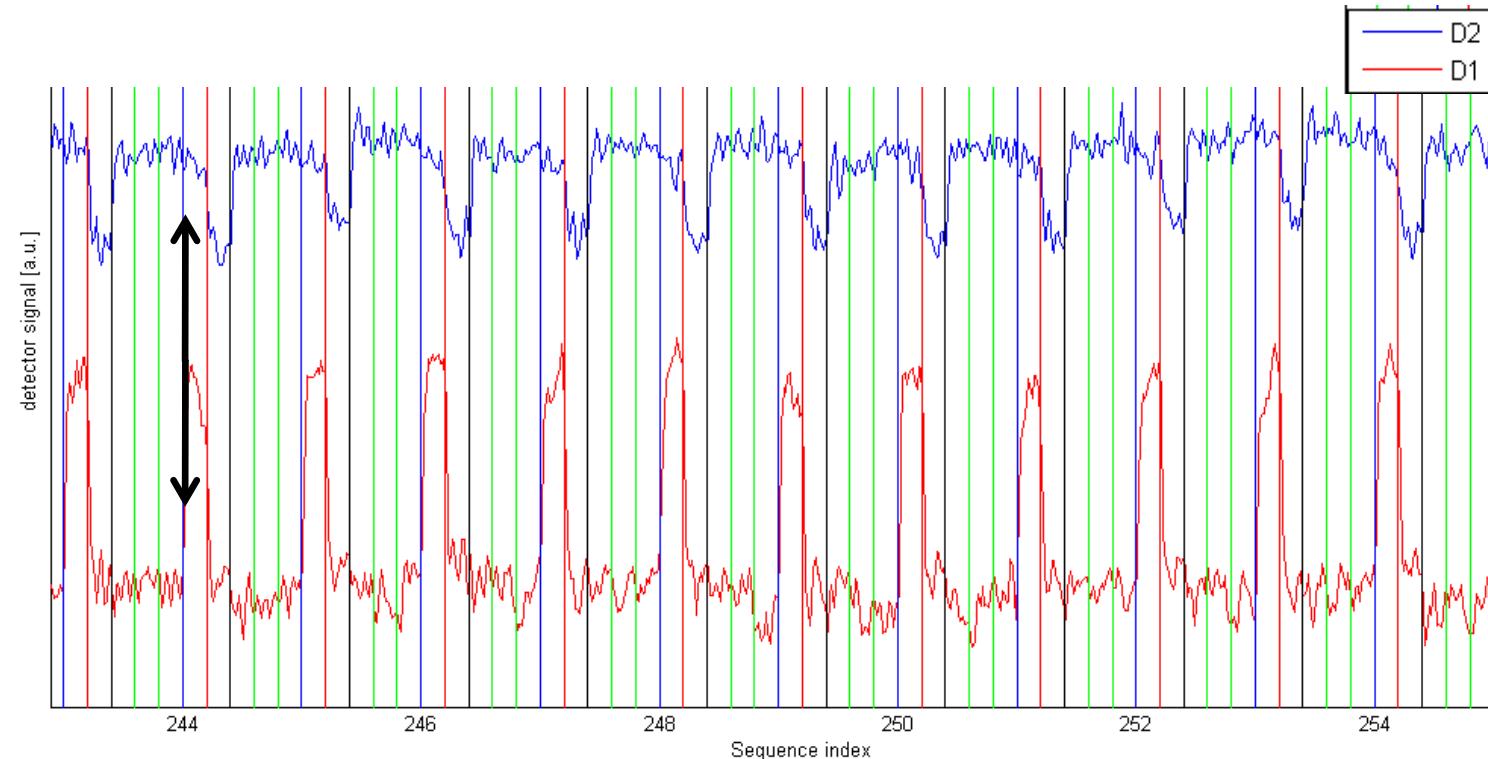




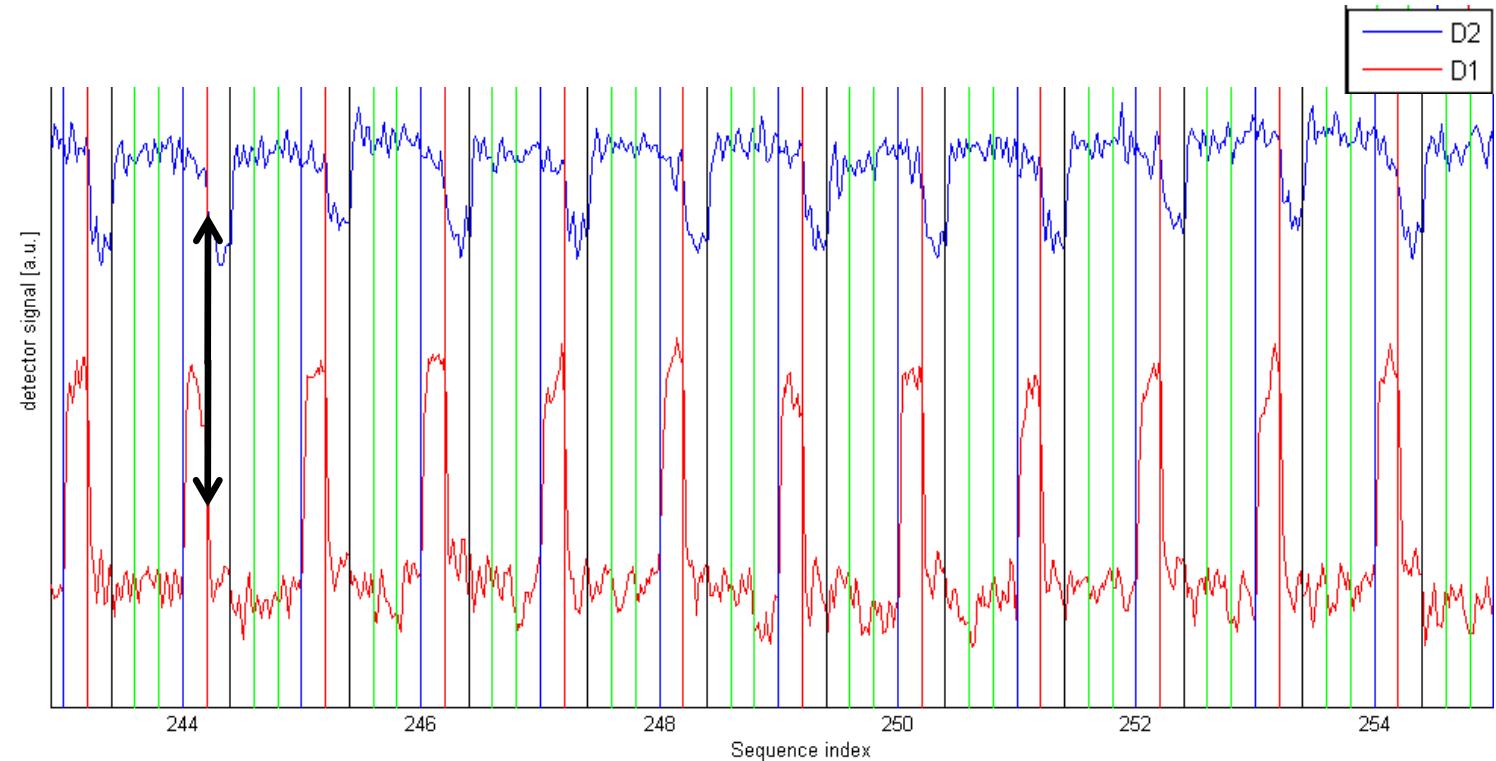
Simultaneous series pumping



Simultaneous series pumping



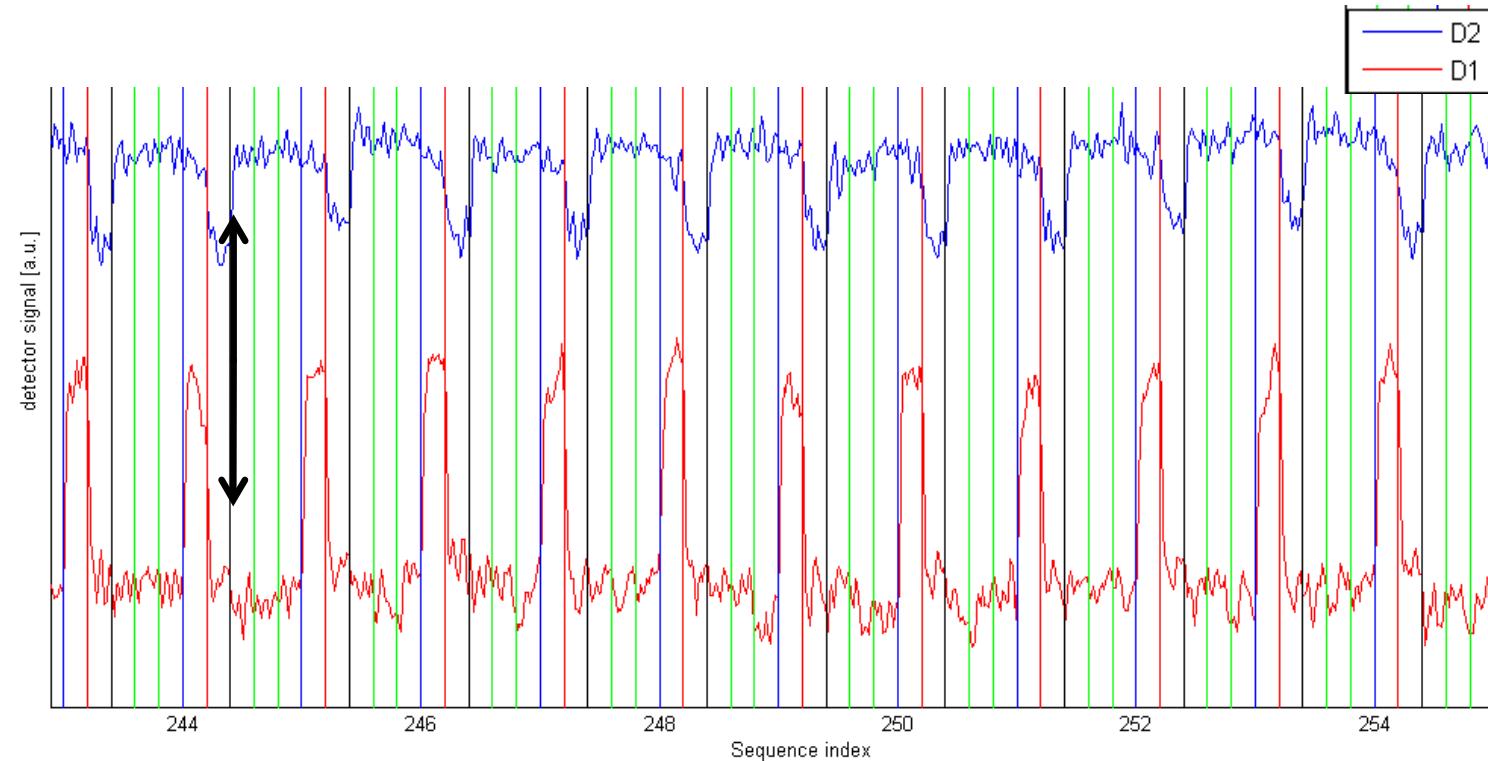
Simultaneous series pumping



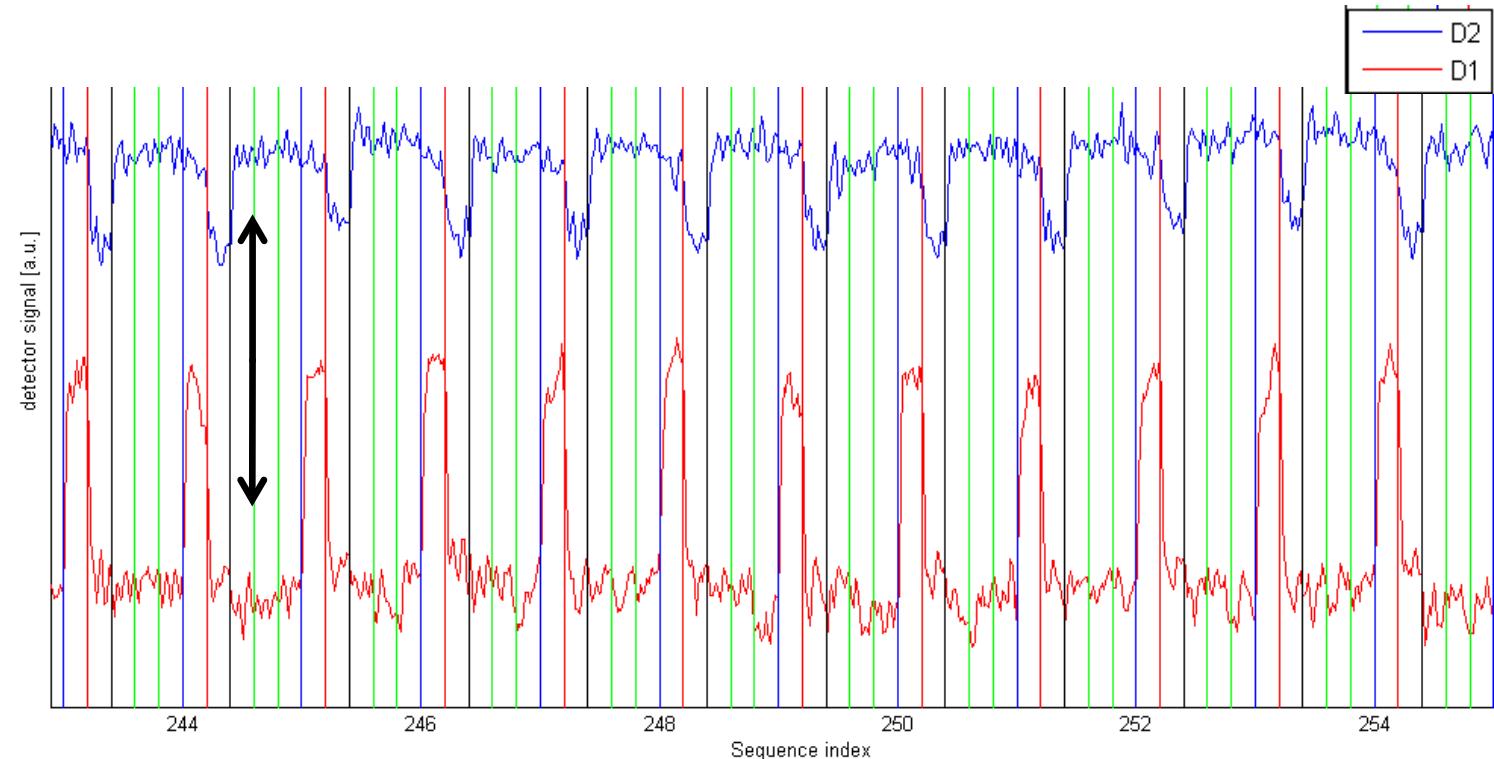


Simultaneous series pumping

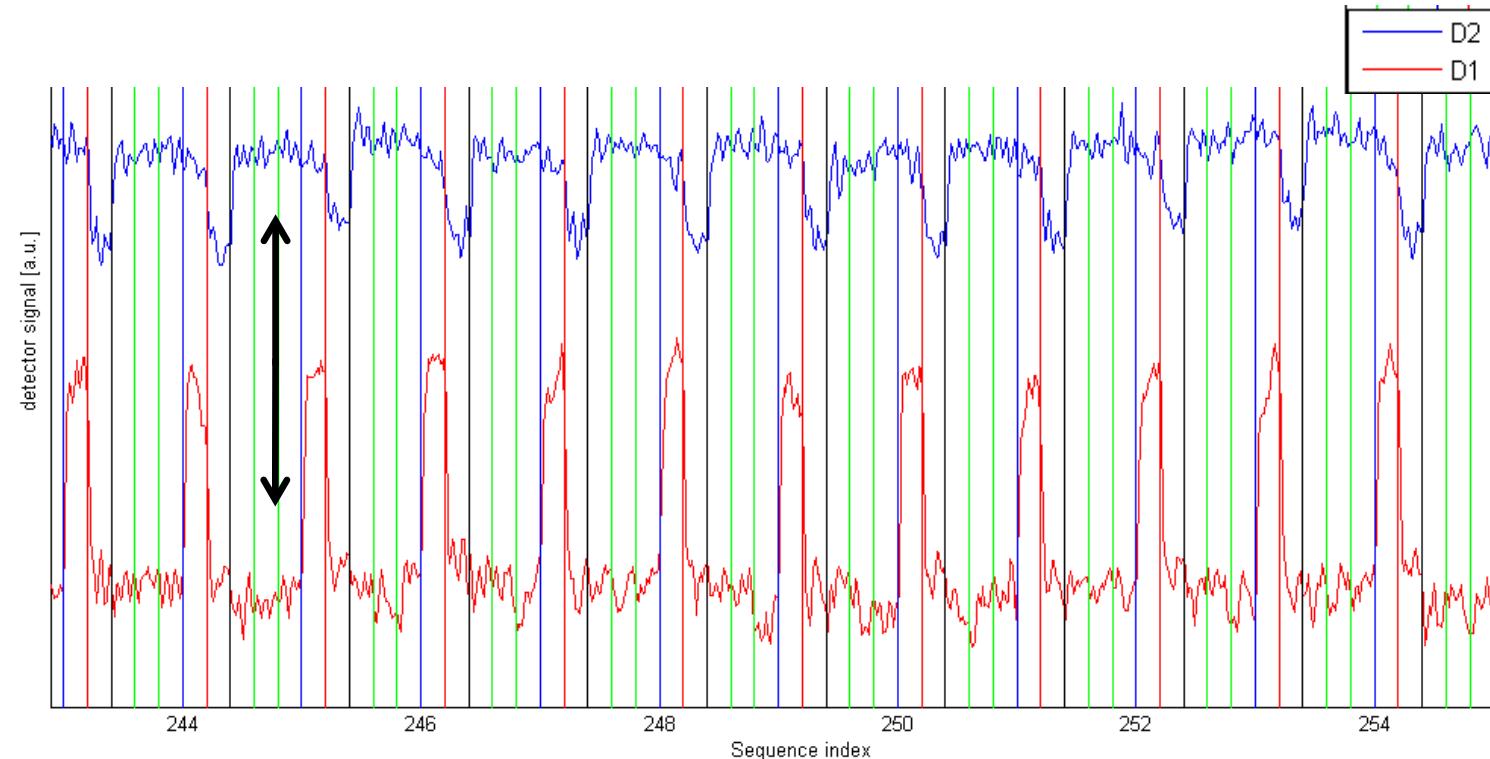
PTB



Simultaneous series pumping

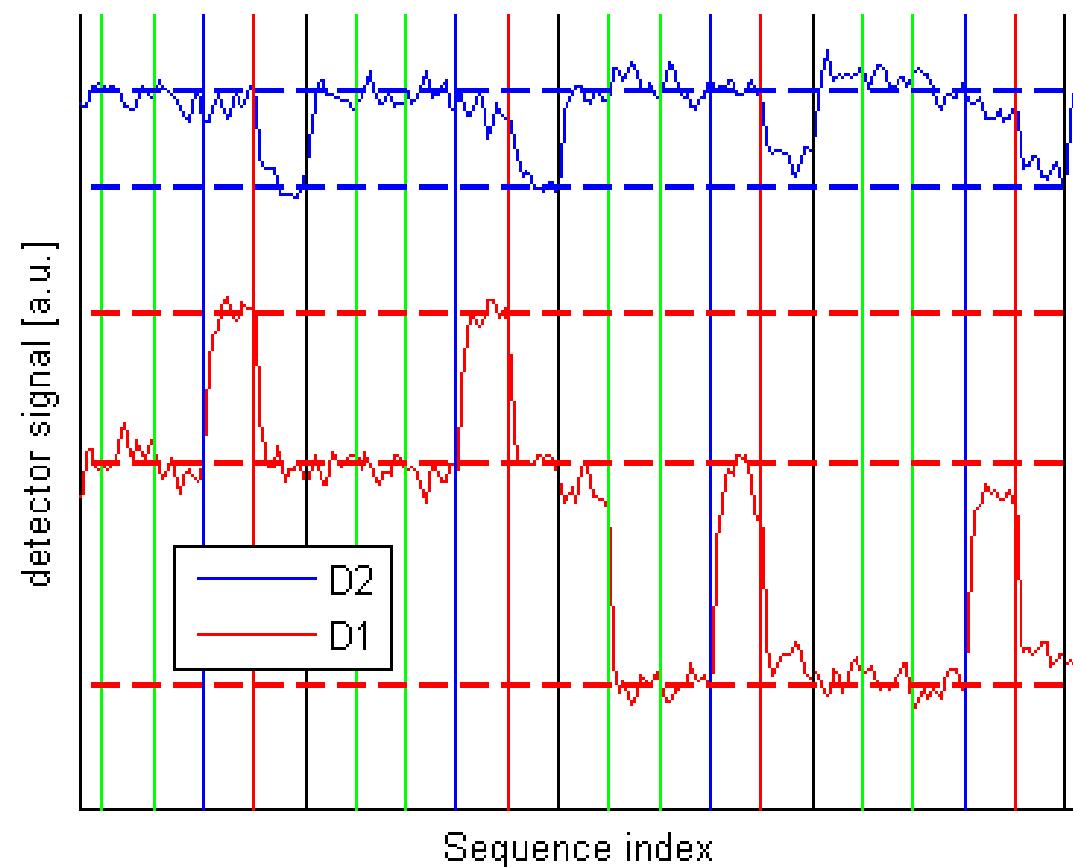


Simultaneous series pumping





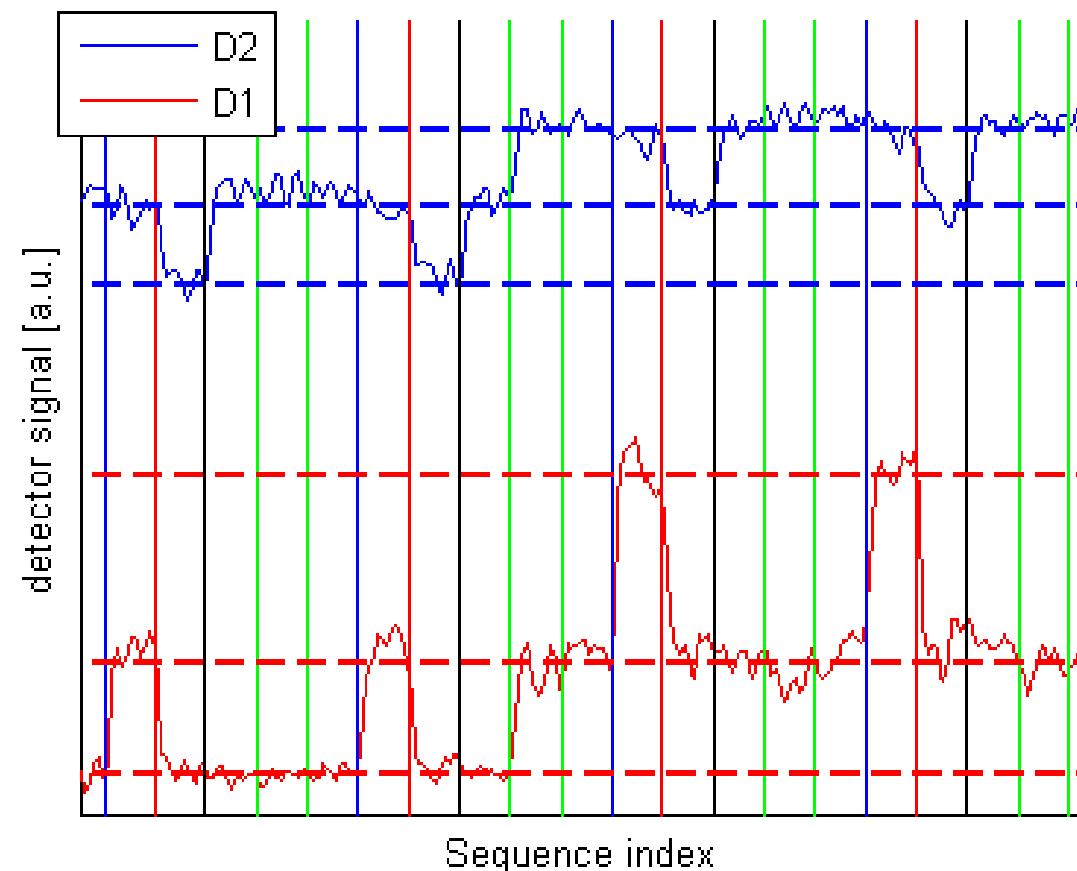
Identification of pump errors



Pump error by P1: Only red SET affected



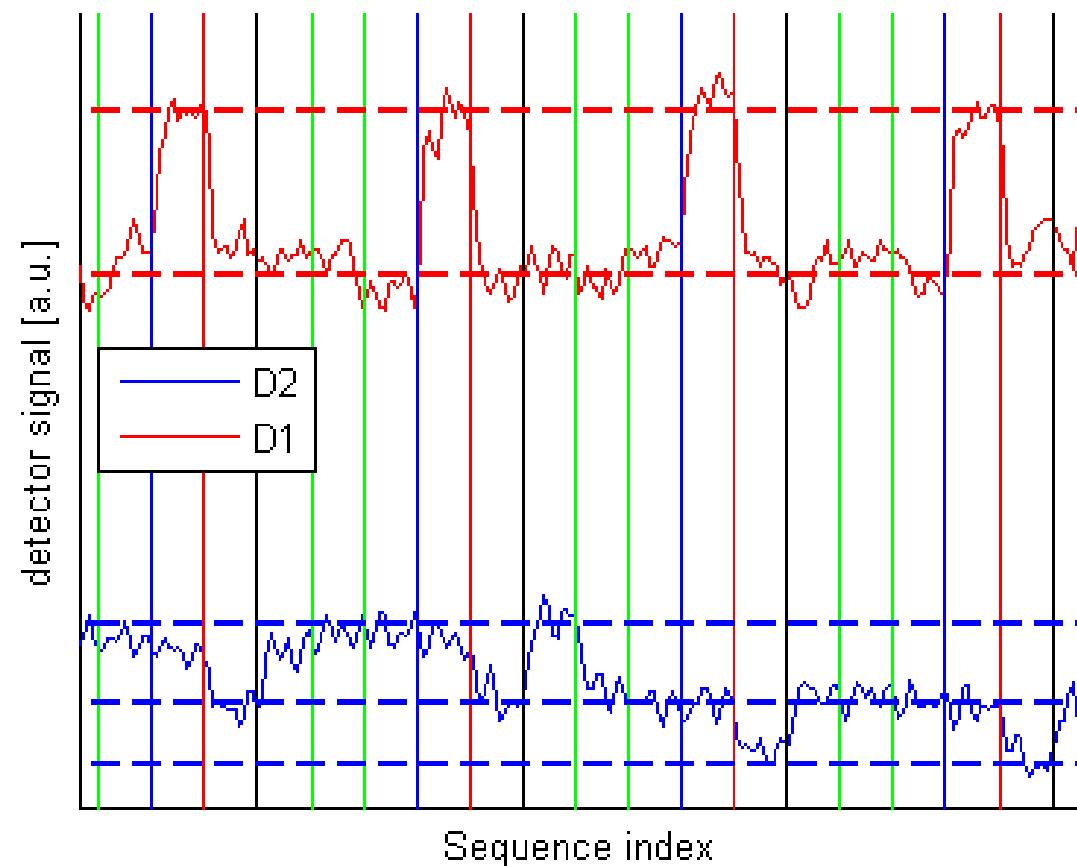
Identification of pump errors



Pump error by P2: Both SETs affected



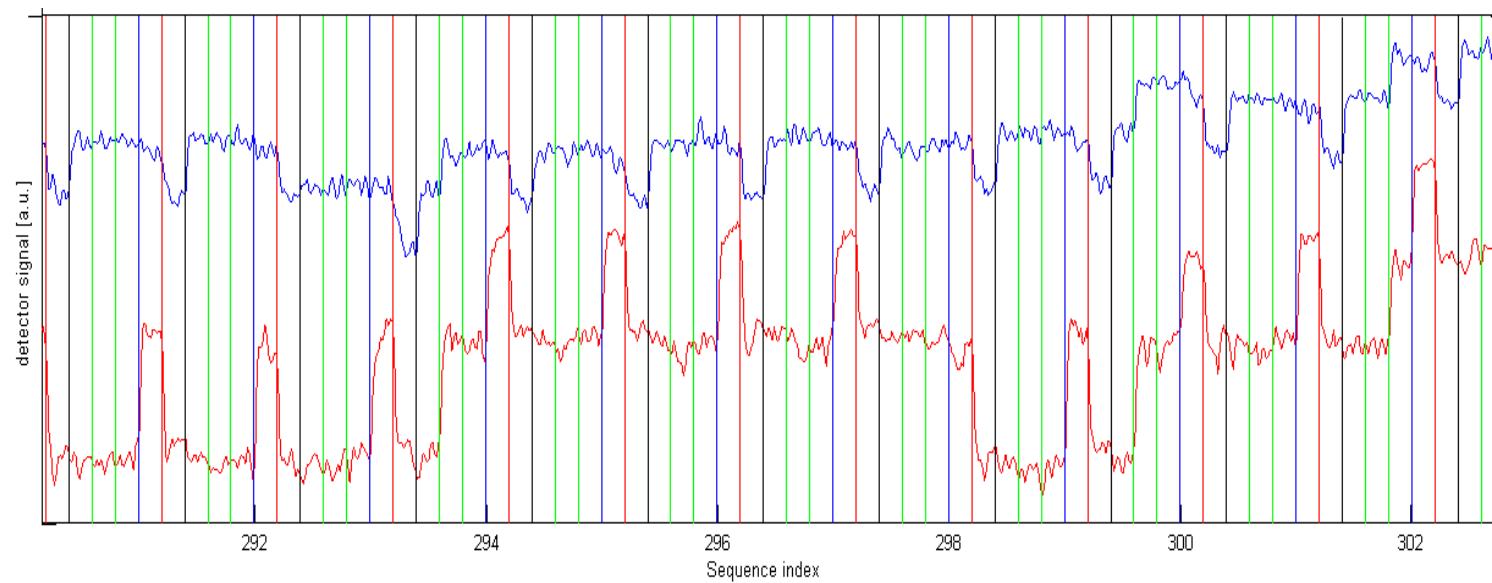
Identification of pump errors



Pump error by P4: Only blue SET affected

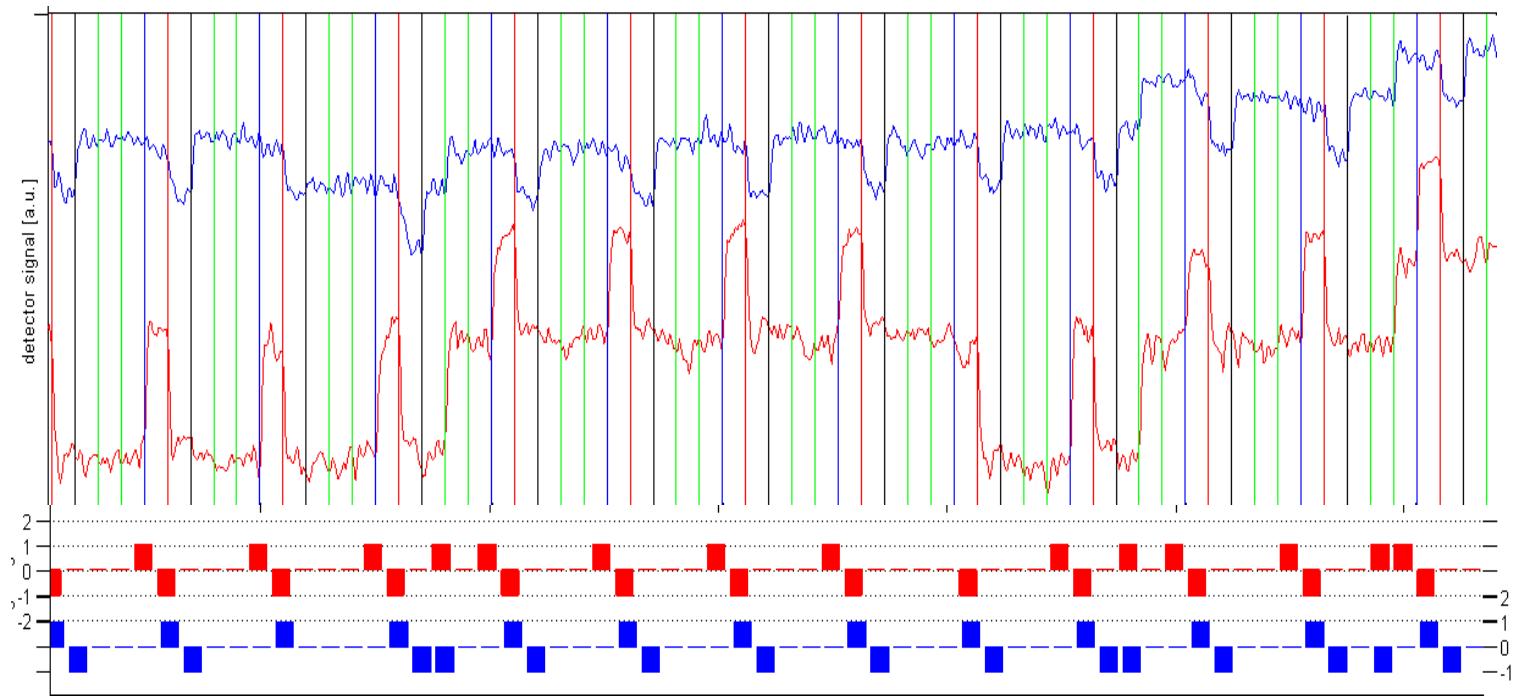


Identification of pump errors

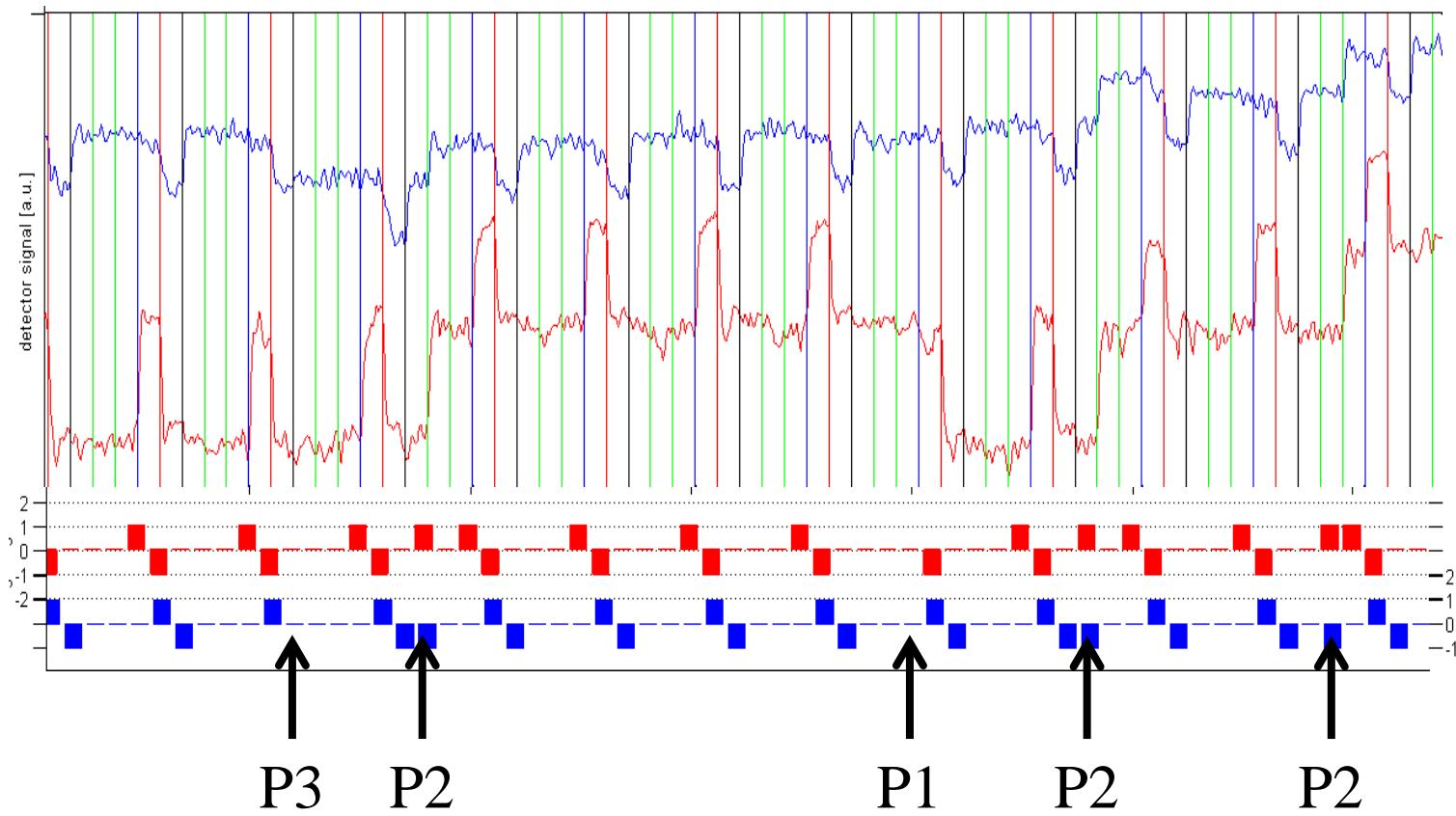




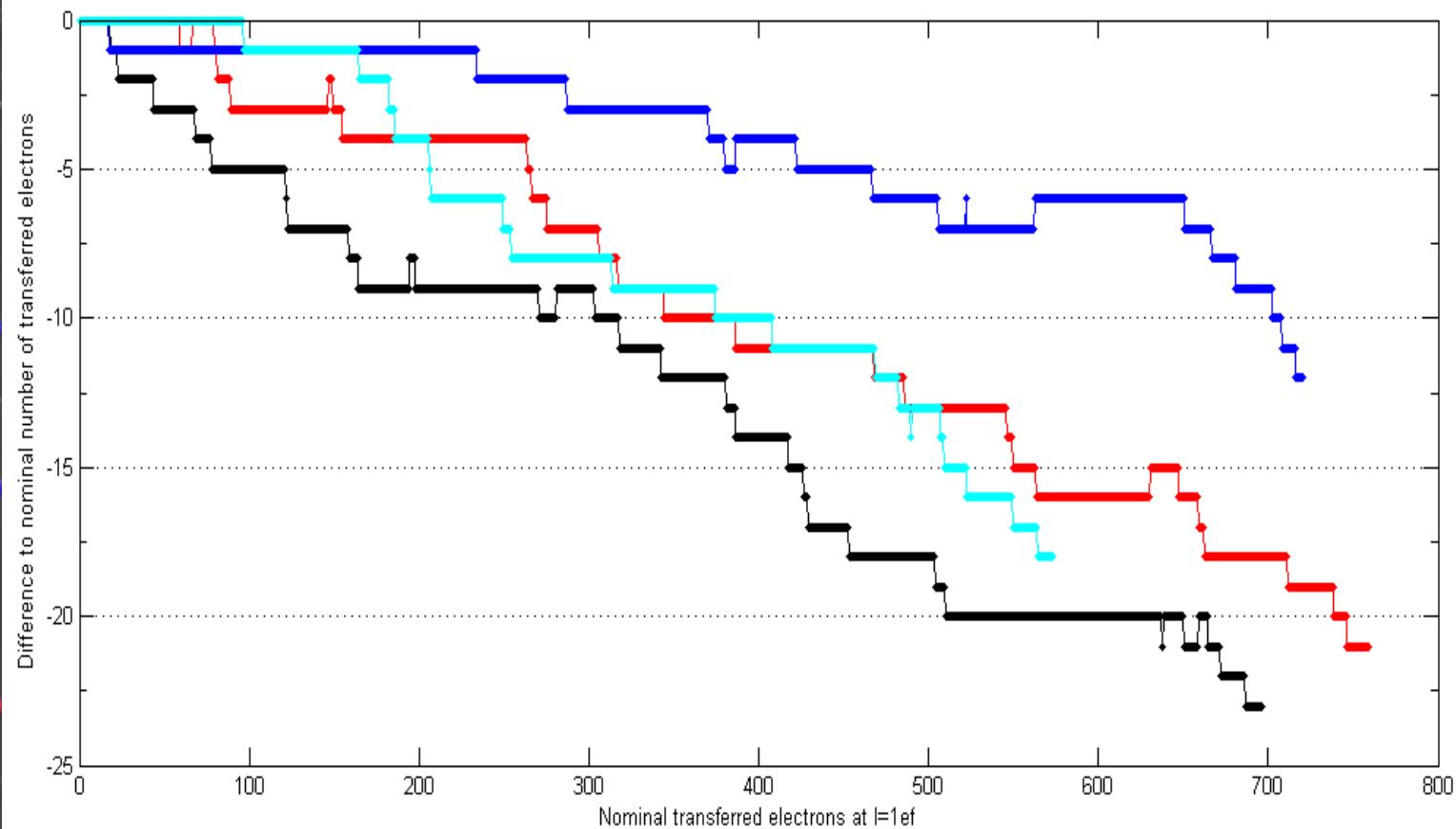
Identification of pump errors



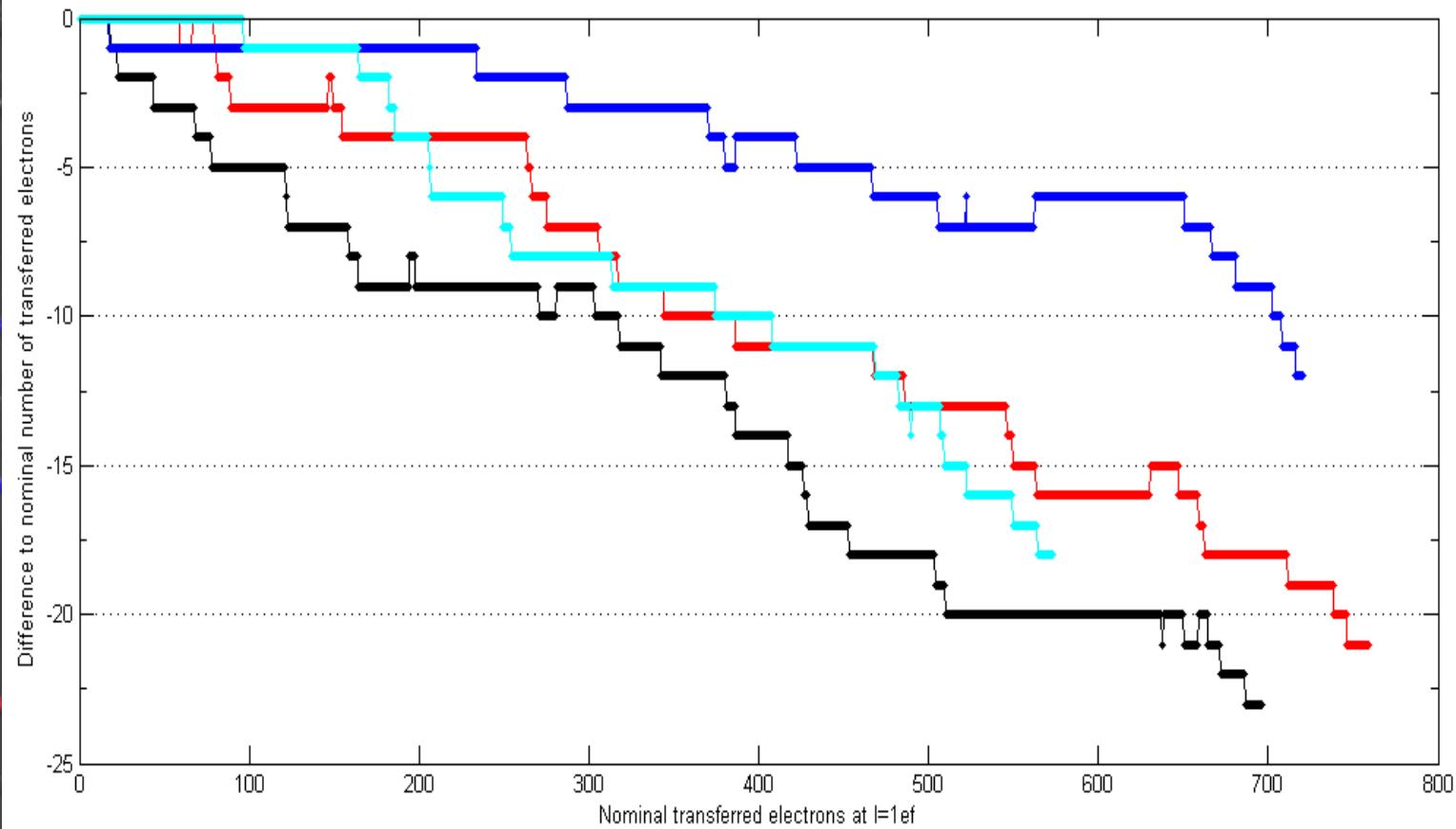
Identification of pump errors



Identification of pump errors

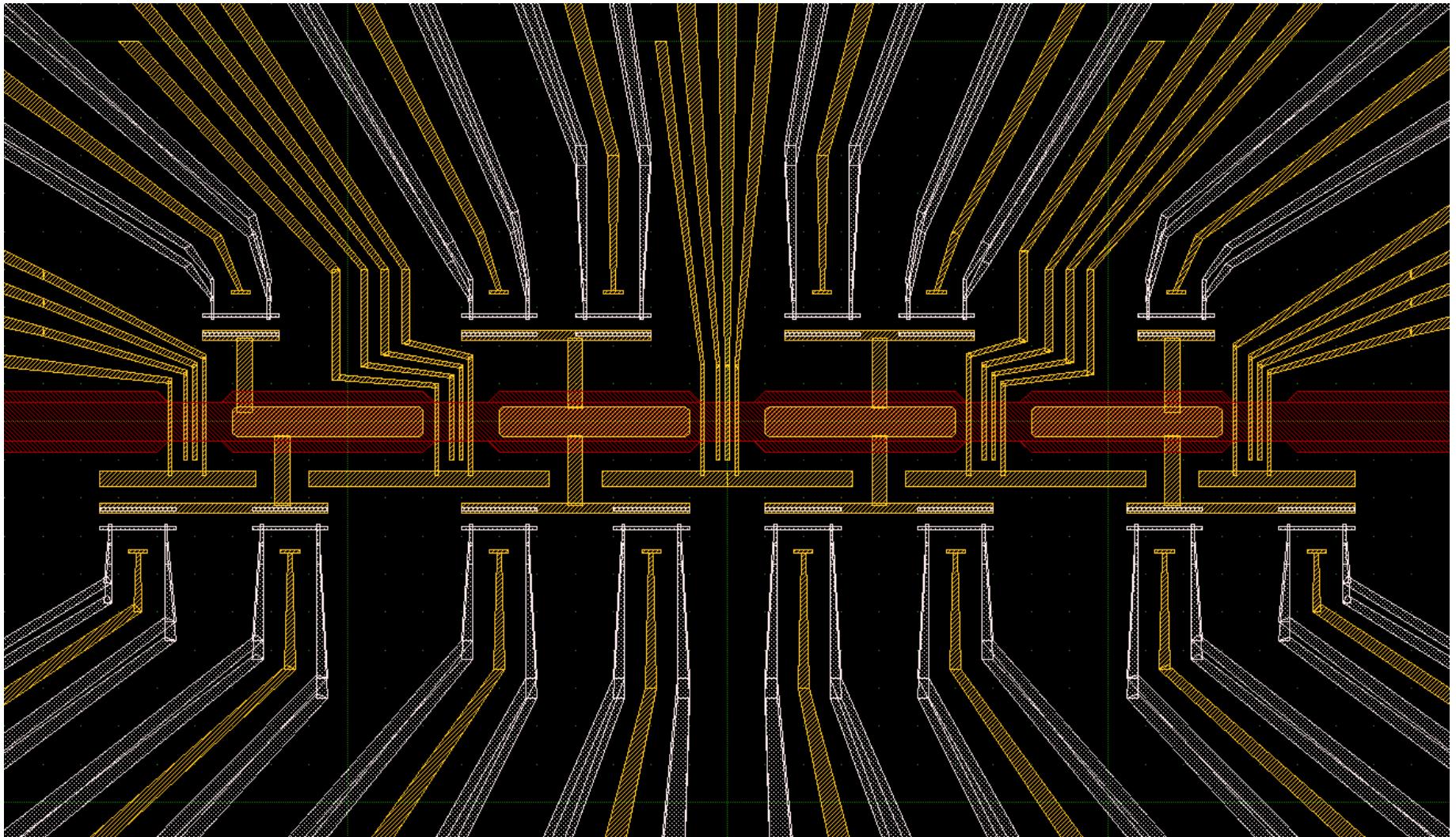


Identification of pump errors



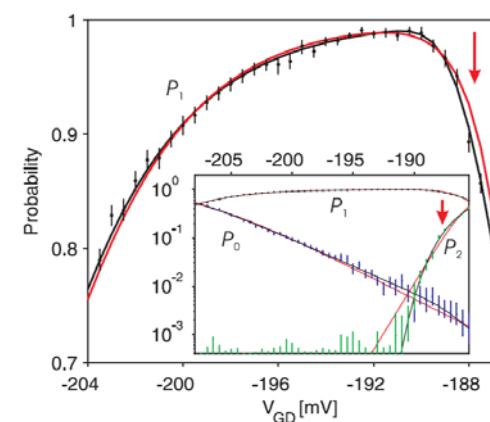
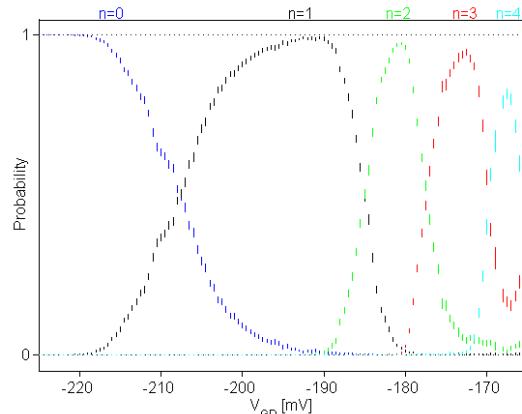
The charge transfer error is reduced by
~2 orders of magnitude by error accounting

New design

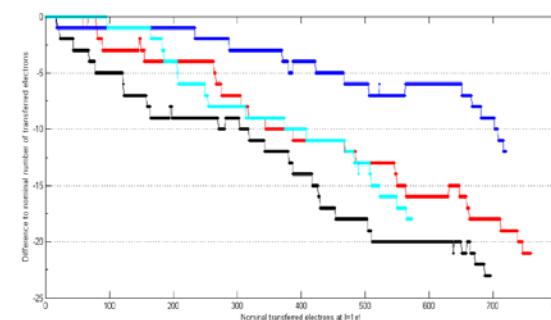
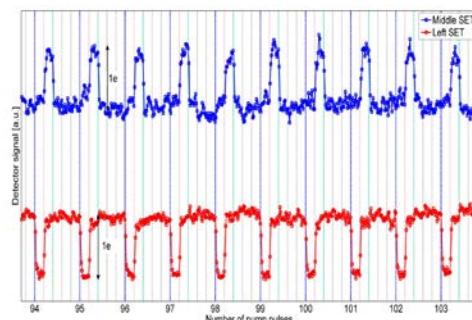


Summary

- Counting measurements on the non-adiabatic electron pump
 - Microscopic insights into the dynamics of electron capture



- First demonstration of a self-referenced current source
 - Road towards error reduction by accounting for (rare) errors



Contributors



Philipp Mirovsky

Bernd Kästner

Frank Hohls

Klaus Pierz

Hans W. Schumacher

Vyacheslavs Kashcheyevs

Janis Timoshenko

Pavel Nazarov

Ralf Dolata

Brigitte Mackrodt

Peter Duda

Thomas Weimann

Peter Hinze

Theoretical treatment of error accounting:

Error accounting algorithm for electron counting experiments

Phys. Rev. B 87, 035312 (2013)

Experiments on counting statistics :

Counting statistics for electron capture in a dynamic quantum dot

Phys. Rev. Lett. 110, 126803 (2013)

Experiments on serial pumps with error detection:

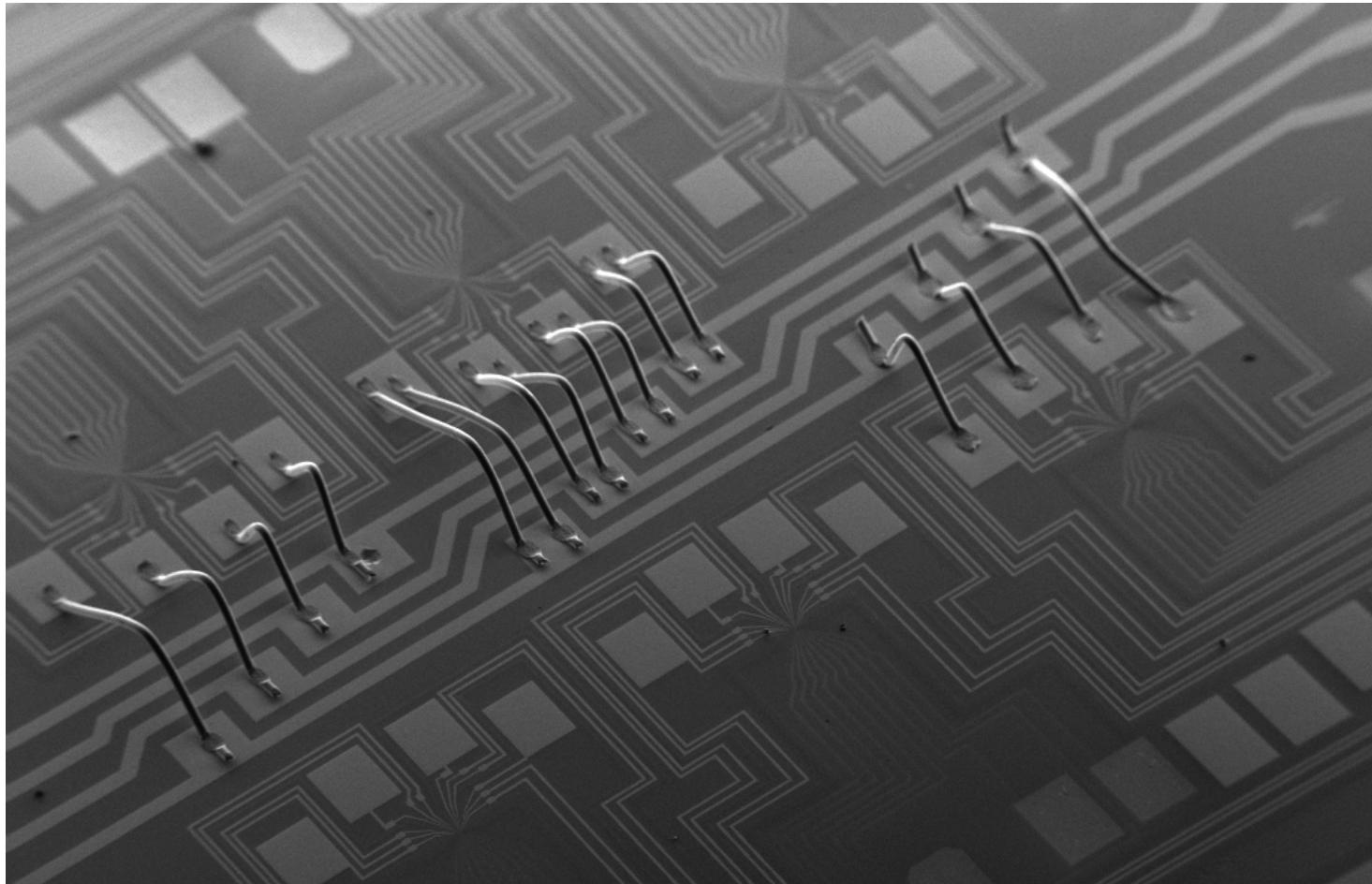
Series Operation of Single-Electron Sources with Charge Detection

CPEM (2012)



Thank you for your attention

PTB



200 µm



Tilt: 40 Grad

EHT = 5.00 kV

WD = 8.6 mm

Signal A = SE2

Mag = 71 X

Date : 17 Apr 2013

Time : 10:48:37

PTB

2.44